### Course Number and Title
**EC1009 ELECTRON DEVICES LAB**

### Credits / Contact Hours
2 / 45

### Instructor Name
Mrs. S. Latha

### Textbooks, References
- LAB MANUAL”, Department of ECE, SRM University

### Purpose
To reinforce learning in the accompanying EC1004 course through hands-on experience by examining the electrical characteristics of various semiconductor devices, such as diodes, BJTs and FETs. To provide the student with the capability to use simulation tools for performing various analysis of semiconductor devices.

### Prerequisites
- Co-requisites
  - EC1004
  - EC1006

### Required, Elective or Selected Elective (as per Table 5.1a)
- Required

### Instructional Objectives
1. To study experimentally the characteristics of diodes, BJT’s and FET’s.
2. To verify practically the response of various special purpose electron devices.
3. To construct and simulate various semiconductor devices using tools such as PSPICE/multisim.

### Student Outcomes from Criterion 3 covered by this Course

<table>
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<th>Student outcome</th>
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### List of Topics Covered

1. Characteristics of PN junction and Zener diode.
2. Input, Output and Transfer characteristics of CE and CC Amplifier.
3. Characteristics of LDR, Photo-diode and Photo transistor.
4. Transfer characteristics of JFET.
5. Transfer characteristics of MOSFET (with depletion and enhancement mode).
6. Characteristics of LED with three different wavelengths.
8. Full wave rectifier with 2 diodes.
9. Full wave rectifier with 4 diodes (Bridge rectifier).
10. Series voltage Regulator.
11. Shunt voltage Regulator.
12. Characteristics of Thermistor.
13. Simulation experiments using PSPICE or Multisim.
Student Outcome

(b) an ability to design and conduct experiments, as well as to analyze and interpret data

Experiment 1 & 2: To verify the VI Characteristics of PN junction diode and Zener diode

Experiment 3: To analyze the Input and Output characteristics and to measure the h-parameter of Common Emitter Configuration.

Experiment 4: To analyze the drain and transfer characteristics of a JFET.

(c) an ability to design a system, component, or process to meet desired needs within realistic constraints such as economic, environmental, social, political, ethical, health and safety, manufacturability, and sustainability

Experiment 5: To verify the distance versus photocurrent characteristics of LDR, Photodiode and Phototransistor

Experiment 6, 7 & 8: To verify the working of a Half wave rectifier, Full wave rectifier and fullwave bridge rectifier and to measure the ripple factor.

Experiment 9 & 10: To design Series and Shunt Voltage regulator. Experiment 11: To verify the VI Characteristics of LED. Experiment 12: To verify the physical characteristics of Thermistor.

(d) an ability to function on multidisciplinary teams

Experiment 6, 7 & 8: To verify the working of a Half wave rectifier, Full wave rectifier and fullwave bridge rectifier and to measure the ripple factor.

Experiment 9 & 10: To design Series and Shunt Voltage regulator

(f) an understanding of professional and ethical responsibility
10: To design Series and Shunt Voltage regulator 
(k) an ability to use the techniques, skills, and modern engineering tools necessary for engineering practice.

Experiment 12: To analyze the input and output characteristics of a transistor in Common Collector Configuration using Pspice Capture Lite Software.

Experiment 13: To analyze the drain characteristics and transfer characteristics of MOSFET using Pspice Capture Lite Software.
S.R.M University  
Faculty of Engineering and Technology  
Department of Electronics and Communication Engineering  

Sub Code : EC1009  
Year/Semester: II / III  
Sub Title : Electron Devices Lab  
Course Time: Jul–Dec’15  
Pre-requisites: EC1004 - Electric Circuits Lab  
Co-requisites: EC1006 - Electron Devices  

Program Education Objective versus Student Outcome

<table>
<thead>
<tr>
<th>Program Educational Objective</th>
<th>PEO1: Graduates will perform as a successful Professional engineer in related fields of Electronics and Communication Engineering.</th>
<th>PEO2: Graduates will pursue higher education and/or engage themselves in continuous professional development to meet global standards.</th>
<th>PEO3: Graduates will work as a team in diverse fields and gradually move into leadership positions.</th>
<th>PEO4: Graduates will understand current professional issues, apply latest technologies and come out with innovative solutions for the betterment of the nation and society.</th>
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### Instructional Objective versus Student Outcome

<table>
<thead>
<tr>
<th>S.No</th>
<th>Instructional Objective</th>
<th>Student Outcome</th>
<th>Experiment Details</th>
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</table>
| 1.   | To study experimentally the characteristics of diodes, BJT’s and FET’s. | (b) an ability to design and conduct experiments, as well as to analyze and interpret data  
(c) an ability to design a system, component, or process to meet desired needs within realistic constraints such as economic, environmental, social, political, ethical, health and safety, manufacturability, and sustainability. | **Experiment 1 & 2:** To verify the VI Characteristics of PN junction diode and Zener diode  
**Experiment 3:** To analyze the Input and Output characteristics and to measure the h-parameter of Common Emitter Configuration.  
**Experiment 4:** To analyze the drain and transfer characteristics of a JFET  
**Experiment 5:** To verify the distance versus photocurrent characteristics of LDR, Photodiode and Phototransistor  
**Experiment 6, 7 & 8:** To verify the working of a Half wave rectifier, Full wave rectifier and full wave bridge rectifier and to measure the ripple factor.  
**Experiment 9 & 10:** To design Series and Shunt Voltage regulator  
**Experiment 11:** To verify the VI Characteristics of LED |
| 2.   | To verify practically the response of various special purpose electron devices. | (c) an ability to design a system, component, or process to meet desired needs within realistic constraints such | **Experiment 8:** To verify the working of a Full wave bridge rectifier and to measure the ripple factor. |
| 3. | To construct and simulate | (k) an ability to use the techniques, skills, and modern engineering tools | **Experiment 12:** analyze the input various semiconductor and output characteristics of a transistor devices using tools such necessary for engineering practice in Common Collector Configuration as PSPICE/multisim using Pspice Capture Lite Software.  
**Experiment 13:** To analyze the drain characteristics and transfer characteristics of MOSFET using Pspice Capture Lite Software.  

|  |  |  | **Experiment 9 & 10:** To design Series and Shunt Voltage regulator  
**Experiment 14:** To verify the physical characteristics of Thermistor.  

|  |  |  | aseconomic, environmental, social, political, ethical, health and safety, manufacturability, and sustainability (d) an ability to function on multidisciplinary teams (f) an understanding of professional and ethical responsibility |
### S.R.M University

**Faculty of Engineering and Technology**

**Department of Electronics and Communication Engineering**

Sub Code : EC1009  
Year/Semester: II / III  
Sub Title : Electron Devices Lab  
Course Time: Jul–Dec’15

Pre-requisites: EC1004 - Electric Circuits Lab  
Co-requisites: EC1006 - Electron Devices

## Experiment Details

<table>
<thead>
<tr>
<th>S.No</th>
<th>Experiment Details</th>
<th>Equipment Required</th>
<th>Components Required</th>
</tr>
</thead>
</table>
| 1    | P-N Junction Diode Characteristics  | 1. Ammeter: (0-30mA), (0-500µA)  
2. Voltmeter : (0-1V) (0-30V)  
3. Regulated Power Supply:(0-30V) | PN Junction diode(IN4001), Resistor (1KΩ) |
| 2    | Zener Diode Characteristics         | 1. Ammeter: (0-30mA), (0-500µA)  
2. Voltmeter : (0-1V) (0-30V)  
3. Regulated Power Supply:(0-30V) | Zener diode(IZ6.2), Resistor (1KΩ) |
| 3    | Common Emitter Configurations       | 1. Ammeter: (0-30mA), (0-500µA)  
2. Voltmeter : (0-1V) (0-30V)  
3. Regulated Power Supply:(0-30V) | BJT(BC147), Resistor(1KΩ) |
| 4    | JFET Characteristics                | 1. Ammeter: (0-30mA), (0-500mA)  
2. Voltmeter : (0-1V) (0-30V)  
3. Regulated Power Supply:(0-30V) | FET(FBW11), Resistor(1KΩ) |
| 5    | Characteristics of LDR, Photodiode, Phototransistor | 1. Ammeter: (0-30mA), (0-500mA)  
2. Voltmeter : (0-1V) (0-30V)  
3. Regulated Power Supply:(0-30V) | Photodiode, Phototransistor and LDR |
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<th>Description</th>
<th>Instrument</th>
<th>Components</th>
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<td>6</td>
<td>Half Wave Rectifier</td>
<td>CRO</td>
<td>Diode(IN4001), Resistor 470Ω, Capacitance 470 µF, Transformar(6-0-6)</td>
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<tr>
<td>7</td>
<td>Full Wave Rectifier</td>
<td>CRO</td>
<td>Diode(IN4001), Resistor 470Ω, Capacitance 470 µF, Transformar(6-0-6)</td>
</tr>
<tr>
<td>8</td>
<td>Full Wave Bridge Rectifier</td>
<td>CRO</td>
<td>Diode(IN4001), Resistor 470Ω, Capacitance 470 µF, Transformar(6-0-6)</td>
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<td>9</td>
<td>Series Voltage Regulator</td>
<td>Multimeter</td>
<td>Power transistor(2N3055), Zener diode(IZ6.2), BJT(BC107), Resistor(947 Ω, 2.48 K Ω, 2.2 K Ω, 2.75K Ω, 49.6 Ω)</td>
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<tr>
<td>10</td>
<td>Shunt Voltage Regulator</td>
<td></td>
<td>Zener diode(IZ5.1), Resistor(31.66 Ω, 10K Ω)</td>
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</table>
| 11| V-I Characteristics Of LED                    | 1. Ammeter: (0-100mA)  
    2. Voltmeter: (0-30V)  
    3. Regulated Power Supply: (0-30V) | LED, Resistor (330 Ω)       |
| 12| Common Collector Configuration Using Pspice   | System with Pspice Capture Lite Software | BJT(BC147), Resistor(1KΩ, 68 KΩ)                                           |
| 13| Characteristics MOSFET Using Pspice           | System with Pspice Capture Lite Software | IRF150                                                                     |
| 14| Characteristics of Thermistor                 | Multimeter | Thermistor, Thermometer                                                    |
EC1009 Laboratory Policies and Report Format

Reports are due at the beginning of the lab period. The reports are intended to be a complete documentation of the work done in preparation for and during the lab. The report should be complete so that someone else familiar with digital design could use it to verify your work. The pre-lab and post-lab report format is as follows:

1. A neat thorough pre-lab must be presented to your course teacher In-charge at the beginning of your scheduled lab period. **Lab reports should be submitted on A4 paper.**

Your report is a professional presentation of your work in the lab. Neatness, organization, timeliness, and completeness will be rewarded. Points will be deducted for any part that is not clear.

2. In this laboratory students will work in teams of three. However, the lab reports will be written individually. Please use the following format for your lab reports.

   a. **Cover Page:** Include your name, Subject Code, Section No., Experiment No. and Date.

   b. **Objectives:** Enumerate 3 or 4 of the topics that you think the lab will teach you. **DO NOT REPEAT** the wording in the lab manual procedures. There should be one or two sentences per objective. Remember, you should write about what you will learn, not what you will do.

   c. **Design:** This part contains all the steps required to arrive at your final circuit. This should include diagrams, tables, equations, theoretical calculation etc. Be sure to reproduce any tables you completed for the lab. **This section should also include a clear written description of your design process.** Simply including a circuit schematic is not sufficient.

   d. **Questions:** Specific questions (Pre-lab and Post-lab) asked in the lab should be answered in the observation notebook. **Retype the questions presented in the lab and then formally answer them.**

3. Your work must be original and prepared independently. However, if you need any guidance or have any questions or problems, please do not hesitate to approach your course teacher in-charge during office hours. The students should follow the dress code in the Lab session.
4. Each laboratory exercise (circuit) must be completed and demonstrated to your course teacher In-charge in order to receive working circuit credit. This is the procedure to follow:
   a. Circuit works: If the circuit works during the lab period (3 hours), call your course teacher in-charge and he/she will sign and date it. This is the end of this lab, and you will get a complete grade for this portion of the lab.
   b. Circuit does not work: If the circuit does not work, you must make use of the open times for the lab room to complete your circuit. When your circuit is ready, contact your staff in-charge to set up a time when the two of you can meet to check your circuit.

5. Attendance at your regularly scheduled lab period is required. An unexpected absence will result in loss of credit for your lab. If for valid reason a student misses a lab, or makes a reasonable request in advance of the class meeting, it is permissible for the student to do the lab in a different section later in the week if approved by the course teacher in-charge of both the sections. Habitually late students (i.e., students late more than 15 minutes more than once) will receive 10 point reductions in their grades for each occurrence following the first.

7. **Reports Due Dates**: Reports are due one week after completion of the corresponding lab.

8. **Systems of Tests**: Regular laboratory class work over the full semester will carry a weightage of 60%. The remaining 40% weightage will be given by conducting an end semester practical examination for every individual student if possible or by conducting a 2 hours duration common written test for all students, based on all the experiment carried out in the semester.

9. **General Procedure**
   a. Properly place the components in the general purpose breadboard and identify the positive and negative terminals of the power supply, before making connection.
   b. Keep the required supply voltage in Power supply and connect power supply voltage and ground terminals to the respective node points in the breadboard.
   c. Connect the components as per the circuit diagram, after verifying connection switch on the supply and note down the required parameter values
   d. After completion of the experiments, switch off the power supply and return the components.
SRM University  
Department of Electronics and Communication Engineering  
EC1009 - Electron Devices Lab  
Laboratory Report Cover sheet  
ODD Semester – 2015

Name : 
Register Number : 
Semester / Section : 
Batch : 
Venue : 
Title of the Experiment : 
Date of Performance : 
Date of Submission :

<table>
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<th>Particulars</th>
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<td>Lab Performance</td>
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<tr>
<td>Post Lab</td>
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</table>

Report Verification

Staff Name : 
Staff Signature :
Contents

Lab 1: P-N JUNCTION DIODE CHARACTERISTICS 1
1.1 Objective
1.2 Hardware Required
1.3 Introduction
1.4 Circuit diagram
   1.4.1 Forward Bias
   1.4.2 Reverse Bias
1.5 Precautions
1.6 Characteristics of PN junction Diode
1.7 Procedure
   1.7.1 Forward Biased Condition
   1.7.2 Reverse biased condition
1.8 Tabular Column
1.9 Model Graph
1.10 Result
1.11 Pre Lab Questions
1.12 Post Lab Questions

Lab 2: ZENER DIODE CHARACTERISTICS 7
2.1 Objective
2.2 Hardware Required
2.3 Introduction
2.4 Circuit diagram
   2.4.1 Forward Bias
   2.4.2 Reverse Bias
   2.4.3 Zener Diode Symbol
2.5 Precautions
2.6 Characteristics of Zener Diode
2.7 Procedure
   2.7.1 Forward Biased Condition
   2.7.2 Reverse biased condition
2.8 Tabular Column
2.9 Model Graph
2.10 Result
2.11 Pre lab Questions
2.12 Post lab Questions

Lab 3: COMMON EMITTER CONFIGURATIONS

3.1 Objective
3.2 Hardware Required
3.3 Introduction
3.4 Pin Assignment
3.5 Circuit Diagram
3.6 Precautions
3.7 Procedure
  3.7.1 Input Characteristics
3.7.2 Output Characteristics
3.8 Tabular Column
3.9 Model Graph
3.10 Result
3.11 Pre lab Questions
3.12 Post lab Questions

Lab 4: JFET CHARACTERISTICS

4.1 Objective
4.2 Hardware Required
4.3 Introduction
4.4 Circuit diagram
4.5 Pin assignment of FET
4.6 Characteristics of JFET
4.7 Precautions
4.8 Tabular Column
4.9 Model Graph
4.10 Calculations from Graph
   4.10.1 Drain Resistance (rd)
   4.10.2 Trans-Conductance (gm)
4.10.3 Amplification Factor (μ)

4.11 Result
4.12 Prelab Questions
4.13 Post lab Questions

Lab5: CHARACTERISTICS OF LDR, PHOTODIODE, PHOTOTRANSISTOR

5.1 Objective
5.2 Hardware Required
5.3 Introduction
  5.3.1 LDR
  5.3.2 Photodiode
  5.3.3 Phototransistor
5.4 Circuit diagram
  5.4.1 LDR
  5.4.2 Photodiode
  5.4.3 Phototransistor
5.5 Tabular Column
5.6 Characteristics of LDR, Photodiode, Phototransistor
5.7 Precautions
5.8 Procedure
5.9 Model Graph
5.10 Result
5.11 Prelab Questions
5.12 Post lab Questions

Lab 6: HALF WAVE RECTIFIER

6.1 Objective
6.2 Hardware Required
6.3 Introduction
6.4 Circuit Diagram of Half Wave Rectifier
6.5 Characteristics of Half Wave Rectifier
6.6 Precautions
6.7 Experiment
6.8 Graph
6.9 Observations
6.10 Result
6.11 Pre Lab
6.12 Post Lab

Lab 7: FULL WAVE RECTIFIER
7.1 Objective
7.2 Hardware Required
7.3 Introduction
7.4 Theoretical calculations
    7.4.1 Ripple Factor
    7.4.2 Efficiency
    7.4.3 Transformer Utilization Factor
7.5 Circuit Diagram
7.6 Model Graph
7.7 Characteristics of Full Wave Rectifier
7.8 Precautions
7.9 Procedure
7.10 Graph Instructions
7.11 Observations
7.12 Result
7.13 Prelab Questions
7.14 Post lab Questions

Lab 8: FULL WAVE BRIDGE RECTIFIER
8.1 Objective
8.2 Hardware Required
8.3 Introduction
8.4 Theoretical calculations
    8.4.1 Ripple Factor
    8.4.2 Efficiency
    8.4.3 Transformer Utilization Factor
8.5 Circuit Diagram
Lab 9: SERIES VOLTAGE REGULATOR

9.1 Objective
9.2 Hardware Required
9.3 Introduction:
   9.3.1 Line Regulation
   9.3.2 Load Regulation
9.4 Circuit Diagram
   9.4.1 Design Specifications
9.5 Characteristics of Series Voltage Rectifier
9.6 Procedure
9.7 Tabulation
9.8 Model Graph
9.9 Result
9.10 Prelab Question
9.11 Post Lab Question

Lab 10: SHUNT VOLTAGE REGULATOR

10.1 Objective
10.2 Hardware Required
10.3 Introduction:
   10.3.1 Line Regulation
   10.3.2 Load Regulation
10.4 Circuit Diagram
10.5 Design
10.6 Characteristics of Shunt Voltage Regulator
10.7 Procedure
   10.7.1 Line regulation
   10.7.2 Load regulation
10.8 Tabulation
10.9 Model Graph
10.10 Result
10.11 Pre Lab Question
10.12 Post Lab Questions

Lab 11: V-I CHARACTERISTICS OF LED

11.1 Objective
11.2 Hardware Required
11.3 Introduction
   11.3.1 Connecting and soldering
   11.3.2 Testing an LED
   11.3.3 Colours of LEDs
   11.3.4 Calculating an LED resistor value
   11.3.5 Connecting LEDs in series
11.4 Circuit diagram
11.5 Procedure
11.6 Tabular column
11.7 Model Graph
11.8 Result
11.9 Pre Lab questions
11.10 Post Lab questions

Lab 12: COMMON COLLECTOR CONFIGURATION USING PSPICE

12.1 Objective
12.2 Hardware Required
12.3 Introduction
12.4 Pin Assignment
12.5 Circuit diagram
12.6 Precautions
12.7 Procedure
12.7.1 Input Characteristics
12.7.2 Output Characteristics

12.8 Model Graph
12.9 Result
12.10 Pre lab Question
12.11 Post lab Questions

Lab 13: CHARACTERISTICS MOSFET USING PSPICE

13.1 Objective
13.2 Theory
    13.2.1 Transfer Characteristics
    13.2.2 Drain Characteristics
13.3 Circuit Diagram
13.4 Handling Precautions
13.5 Model Graph
13.6 Result
13.7 Pre lab Questions
13.8 Post lab Questions

EXP 14: CHARACTERISTICS OF THERMISTOR

14.1 Objective
14.2 Hardware Required
14.3 Introduction
14.4 Experimental Set up
14.5 Procedure
14.6 Tabular column
14.7 Model graph
14.8 Result
14.9 Pre Lab Questions
14.10 Post Lab Questions
EXP 1 P-N JUNCTION DIODE CHARACTERISTICS

1.1 Objective:

To study the Volt-Ampere Characteristics of Silicon P-N Junction Diode and to find cut-in voltage, static and dynamic resistances.

1.2 Hardware Required:

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<th>Quantity</th>
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<tr>
<td>01</td>
<td>PN Junction Diode</td>
<td>1N4001</td>
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<tr>
<td>02</td>
<td>Resistance</td>
<td></td>
<td>1k ohm, 10% tolerance, 1/2 watt rating</td>
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<tr>
<td>03</td>
<td>Regulated power supply</td>
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<td>(0 – 30V), 2A Rating</td>
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<tr>
<td>04</td>
<td>Ammeter</td>
<td>MC</td>
<td>(0-30)mA, (0-500)μA</td>
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<td>Voltmeter</td>
<td>MC</td>
<td>(0 – 1)V, (0 – 30)V</td>
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<tr>
<td>06</td>
<td>Bread board and</td>
<td></td>
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<tr>
<td></td>
<td>connecting wires</td>
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1.3 Introduction:

Donor impurities (pentavalent) are introduced into one-side and acceptor impurities into the other side of a single crystal of an intrinsic semiconductor to form a p-n diode with a junction called depletion region (this region is depleted off the charge carriers). This region gives rise to a potential barrier \( V_\gamma \) called Cut-in Voltage. This is the voltage across the diode at which it starts conducting. The P-N junction can conduct beyond this Potential.

The P-N junction supports uni-directional current flow. If +ve terminal of the input supply is connected to anode (P-side) and –ve terminal of the input supply is connected to cathode (N-side), then diode is said to be forward biased. In this condition the height of the potential barrier at the junction is lowered by an amount equal to given forward biasing voltage.

Both the holes from p-side and electrons from n-side cross the junction simultaneously and constitute a forward current (injected minority current – due to holes crossing the junction and entering N-side of the diode, due to electrons crossing the junction and entering P-side of the diode). Assuming current flowing through the
diode to be very large, the diode can be approximated as short-circuited switch. If –ve terminal of the input supply is connected to anode (p-side) and +ve terminal of the input supply is connected to cathode (n-side) then the diode is said to be reverse biased. In this condition an amount equal to reverse biasing voltage increases the height of the potential barrier at the junction.

Both the holes on p-side and electrons on n-side tend to move away from the junction thereby increasing the depleted region. However the process cannot continue indefinitely, thus a small current called **reverse saturation current** continues to flow in the diode. This small current is due to thermally generated carriers. Assuming current flowing through the diode to be negligible, the diode can be approximated as an open circuited switch.

The volt-ampere characteristics of a diode explained by following equation:

\[ I = I_o \left( \exp \left( \frac{V}{\eta V_T} \right) - 1 \right) \]

- \( I \)=current flowing in the diode
- \( I_o \)=reverse saturation current
- \( V \)=voltage applied to the diode
- \( V_T \)=volt-equivalent of temperature=\( kT/q = T/11,600 = 26mV(@ \text{room temp}) \).
- \( \eta \)=1 (for Ge) and 2 (for Si)

Germanium diode has smaller cut-in-voltage than Silicon diode. The reverse saturation current in Ge diode is larger in magnitude when compared to silicon diode.

1.4 Circuit diagram: 1.4.1 Forward Bias

![Forward Bias Circuit Diagram]

1.4.2 Reverse Bias

![Reverse Bias Circuit Diagram]
1.5 Precautions:
1. While doing the experiment do not exceed the ratings of the diode. This may lead to damage of the diode.
2. Connect voltmeter and Ammeter in correct polarities as shown in the circuit diagram.
3. Do not switch ON the power supply unless you have checked the circuit connections as per the circuit diagram.

1.6 Characteristics of PN junction diode:
1. Breakdown voltage can be traded with switching speed. A reduction in recombination lifetime through addition of suitable impurities will increase leakage current. This can be countered by decreasing diode area which however will lead to reduced forward current rating unless doping is increased. This will lead to a reduced breakdown voltage.
2. The breakdown voltage and reverse recovery are also related together in more direct manner. Regions which have higher doping also have a lower recombination lifetime so that a lower breakdown voltage diode is likely to have lower lifetime and better switching speeds. So a single diode cannot meet the diverse applications.

1.7 Procedure:
1.7.1 Forward Biased Condition:
1. Connect the PN Junction diode in forward bias i.e. Anode is connected to positive of the power supply and cathode is connected to negative of the power supply.
2. Use a Regulated power supply of range (0-30) V and a series resistance of 1kΩ.
3. For various values of forward voltage (Vf) note down the corresponding values of forward current (If).

1.7.2 Reverse biased condition:
4. Connect the PN Junction diode in Reverse bias i.e; anode is connected to negative of the power supply and cathode is connected to positive of the power supply.
5. For various values of (Vr) note down the corresponding values of reverse current (Ir).
1.8 Tabular column:

1.8.1 Forward Bias:

<table>
<thead>
<tr>
<th>S. No</th>
<th>$V_f$ (volts)</th>
<th>$I_f$ (mA)</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

1.8.2 Reverse Bias:

<table>
<thead>
<tr>
<th>S. No</th>
<th>$V_r$ (volts)</th>
<th>$I_r$ (μA)</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
1.9 Model Graph:

1.10 Result:
Thus the VI characteristic of PN junction diode was verified.

i. Cut in voltage = ........ V

ii. Static forward Resistance $R_{dc} = (V_f/I_f)$ Ω

iii. Dynamic forward Resistance $r_{ac} = (\Delta V_f/\Delta I_f)$ Ω

iv. Static Reverse Resistance $R_{dc} = (V_r/I_r)$ Ω

v. Dynamic Reverse Resistance $r_{ac} = (\Delta V_r/\Delta I_r)$ Ω

1.11 Prelab Questions:
1. What is the need for doping?
2. How depletion region is formed in the PN junction?
3. What is break down voltage?
4. What is cut-in or knee voltage? Specify its value in case of Ge or Si?
5. What are the differences between Ge and Si diode?
6. What is the relationship between depletion width and the concentration of impurities?
1.12 Post lab Questions:

1. Generate input and output characteristics in PN Junction diode using PSPICE and compare with the obtained output.
2. How does PN-junction diode acts as a switch?
3. Comment on diode operation under zero biasing condition.
4. For a uniformly doped silicon PN junction diode with an N-type doping of $10^{16}$ cm$^{-3}$ and a P-type doping of $2 \times 10^{16}$ cm$^{-3}$, Sketch the potential within the space charge region at equilibrium. What fraction of the built-in voltage is dropped in the N-region? Where will most of the built-in voltage be dropped if the P type doping is much larger than the N-type doping?
5. The depletion capacitance/Area measured for a symmetrical Silicon PN junction at different bias voltage is given below:

<table>
<thead>
<tr>
<th>Bias</th>
<th>Capacitance (F/cm$^2$)</th>
</tr>
</thead>
<tbody>
<tr>
<td>0.25</td>
<td>3x10$^{-8}$</td>
</tr>
<tr>
<td>0.0</td>
<td>2.44x10$^{-8}$</td>
</tr>
<tr>
<td>-0.5</td>
<td>1.86x10$^{-8}$</td>
</tr>
<tr>
<td>-0.7</td>
<td>1.72x10$^{-8}$</td>
</tr>
</tbody>
</table>

(a) Determine the doping of N and P-regions
(b) Determine the built-in voltage
(c) Determine the depletion width at zero bias
6. Design circuits to get the following outputs.
EXP 2: ZENER DIODE CHARACTERISTICS

2.1 Objective:

To study the Volt-Ampere characteristics of Zener diode and to measure the Zener break down voltage.

2.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>01</td>
<td>Zener Diode</td>
<td>IZ 6.2</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>02</td>
<td>Resistance</td>
<td></td>
<td>1k ohm, 10% tolerance, 1/2 watt rating</td>
<td>1</td>
</tr>
<tr>
<td>03</td>
<td>Regulated power supply</td>
<td></td>
<td>(0 – 30V), 2A rating</td>
<td>1</td>
</tr>
<tr>
<td>04</td>
<td>Ammeter mC</td>
<td></td>
<td>(0-30)mA</td>
<td>1</td>
</tr>
<tr>
<td>05</td>
<td>Voltmeter mC</td>
<td></td>
<td>(0 – 1)V, (0 – 10)V</td>
<td>1</td>
</tr>
<tr>
<td>06</td>
<td>Bread board and connecting wires</td>
<td></td>
<td></td>
<td>1</td>
</tr>
</tbody>
</table>

2.3 Introduction:

An ideal P-N Junction diode does not conduct in reverse biased condition. A Zener diode conducts excellently even in reverse biased condition. These diodes operate at a precise value of voltage called break down voltage. A Zener diode when forward biased behaves like an ordinary P-N junction diode. A Zener diode when reverse biased can either undergo avalanche breakdown or Zener breakdown.

Avalanche breakdown:-If both p-side and n-side of the diode are lightly doped, depletion region at the junction widens. Application of a very large electric field at the junction may rupture covalent bonding between electrons. Such rupture leads to the generation of a large number of charge carriers resulting in avalanche multiplication.

Zener breakdown:-If both p-side and n-side of the diode are heavily doped, depletion region at the junction reduces. Application of even a small voltage at the
junction ruptures covalent bonding and generates large number of charge carriers. Such sudden increase in the number of charge carriers results in Zener mechanism.

2.4 Circuit diagram: 2.4.1 Forward Bias

![Forward Bias Circuit Diagram](image1)

2.4.2 Reverse Bias

![Reverse Bias Circuit Diagram](image2)

2.4.3 Zener Diode Symbol:

![Zener Diode Symbol](image3)

2.5 Precautions:
1. While doing the experiment do not exceed the ratings of the diode. This may lead to damage of the diode.
2. Connect voltmeter and Ammeter in correct polarities as shown in the circuit diagram.
3. Do not switch ON the power supply unless you have checked the circuit connections as per the circuit diagram.
2.6 Characteristics of Zener Diode:
For IZ6.2 Zener diode,

Forward Bias:
At a given (constant) diode current, V exhibits an approximately linear shift in the VI-characteristic due to the combined effect of the temperature dependences of both $I_s$ and $V_T$.
Typically, the VI-characteristic shifts approximately -2 mV/°C.

Reverse Bias:
The temperature dependence of the reverse current is that of $I_s$ alone, which changes exponentially as a function of temperature. Typically, $I_s$ approx. doubles for every 10 °C increase in Temperature. These variations may lead to significant changes in the operation of a circuit over a large temperature range and, in many applications, requires compensation strategies to be implemented in the design of some circuits.

2.7 Procedure:
2.7.1 Forward Biased Condition:
1. Connect the Zener diode in forward bias i.e; anode is connected to positive of the power supply and cathode is connected to negative of the power supply as in circuit.
2. Use a Regulated power supply of range (0-30) V and a series resistance of 1kΩ.
3. For various values of forward voltage ($V_f$) note down the corresponding values of forward Current ($I_f$).

2.7.2 Reverse biased condition:
1. Connect the Zener diode in Reverse bias i.e; anode is connected to negative of the power supply and cathode is connected to positive of the power supply as in circuit.
2. For various values of reverse voltage ($V_r$) note down the corresponding values of reverse current ($I_r$).
2.8 Tabular column: 2.8.1 Forward Bias:

<table>
<thead>
<tr>
<th>S. No</th>
<th>$V_f$ (volts)</th>
<th>$I_f$ (mA)</th>
</tr>
</thead>
</table>

2.8.2 Reverse Bias:

<table>
<thead>
<tr>
<th>S. No</th>
<th>$V_r$ (volts)</th>
<th>$I_r$ (mA)</th>
</tr>
</thead>
</table>
2.9 Model Graph:

![Graph of Zener Diode Characteristics]

2.10 Result:

The Zener diode characteristics have been verified and the following parameters were calculated
i) Cut in voltage = ........ V
ii) Break down voltage = .......... V

2.11 Pre lab Questions:
1. Explain the concept of Zener breakdown?
2. How depletion region gets thin by increasing doping level in Zener diode?
3. State the reason why an ordinary diode suffers avalanche breakdown rather than Zener breakdown?
4. Give the reasons why Zener diode acts as a reference element in the voltage regulator circuits.
5. What type of biasing must be used when a Zener diode is used as a regulator?

2.12 Post lab Questions:
1. Generate input and output characteristics in Zener diode using PSPICE and compare with the obtained output.
2. Design a DC power supply network using Zener diode.
3. What happens when the Zener diodes are connected in series?

4. Justify the use of zener diode in a stabilization circuit?

5. How will you differentiate the diodes whether it is Zener or avalanche when you are given two diodes of rating 6.2 V and 24V?

6. How does a zener diode protect meters from excess voltage that is applied accidentally?
EXP 3: COMMON EMITTER CONFIGURATIONS

3.1 Objective:

To study the input and output characteristics of a bipolar junction transistor in Common Emitter configuration and to measure h-parameters

3.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>01</td>
<td>Transistor</td>
<td>BC147</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>02</td>
<td>Resistance</td>
<td></td>
<td>1k ohm, 10% tolerance, 1/2 watt rating</td>
<td>2</td>
</tr>
<tr>
<td>03</td>
<td>Regulated power supply</td>
<td></td>
<td>(0 – 30V), 2A Rating</td>
<td>2</td>
</tr>
<tr>
<td>04</td>
<td>Ammeter</td>
<td>MC</td>
<td>(1-30)mA, (0-500)μA</td>
<td>1</td>
</tr>
<tr>
<td>05</td>
<td>Voltmeter</td>
<td>MC</td>
<td>(0 – 1)V, (0 – 30)V</td>
<td>1</td>
</tr>
<tr>
<td>06</td>
<td>Bread board and connecting wires</td>
<td></td>
<td></td>
<td>1</td>
</tr>
</tbody>
</table>

3.3 Introduction:

Bipolar junction transistor (BJT) is a 3 terminal (emitter, base, collector) semiconductor device. There are two types of transistors namely NPN and PNP. It consists of two P-N junctions namely emitter junction and collector junction.

In Common Emitter configuration the input is applied between base and emitter and the output is taken from collector and emitter. Here emitter is common to both input and output and hence the name common emitter configuration.

Input characteristics are obtained between the input current and input voltage taking output voltage as parameter. It is plotted between $V_{BE}$ and $I_B$ at constant $V_{CE}$.
in CE configuration.

Output characteristics are obtained between the output voltage and output current taking input current as parameter. It is plotted between $V_{CE}$ and $I_C$ at constant $I_B$ in CE configuration.

3.4 Pin Assignment:

![Transistor Pin Assignment Diagram]

3.5 Circuit Diagram:

![Transistor Circuit Diagram]

3.6 Precautions:

1. While doing the experiment do not exceed the ratings of the transistor. This may lead to damage the transistor.
2. Connect voltmeter and Ammeter in correct polarities as shown in the circuit diagram.
3. Do not switch ON the power supply unless you have checked the circuit connections as per the circuit diagram.
4. Make sure while selecting the emitter, base and collector terminals of the transistor.
3.7 Procedure:

3.7.1 Input Characteristics
1. Connect the transistor in CE configuration as per circuit diagram.
2. Keep output voltage $V_{CE} = 0$V by varying $V_{CC}$.
3. Varying $V_{BB}$ gradually, note down both base current $I_B$ and base-emitter voltage ($V_{BE}$).
4. Repeat above procedure (step 3) for various values of $V_{CE}$.

3.7.2 Output Characteristics
1. Make the connections as per circuit diagram.
2. By varying $V_{BB}$ keep the base current $I_B = 20 \mu$A.
3. Varying $V_{CC}$ gradually, note down the readings of collector-current ($I_C$) and collector-emitter voltage ($V_{CE}$).
4. Repeat above procedure (step 3) for different values of $I_E$.

3.8 Tabular Column:

3.8.1 Input Characteristics:

<table>
<thead>
<tr>
<th>$V_{CE} = 0$ V</th>
<th>$V_{CE} = 4$V</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{BE}$ (volts)</td>
<td>$I_B$ (mA)</td>
</tr>
<tr>
<td>----------------</td>
<td>-------------</td>
</tr>
</tbody>
</table>
3.8.2 Output Characteristics:

<table>
<thead>
<tr>
<th>$I_B$</th>
<th>$I_B = 30 \mu A$</th>
<th>$I_B = 60 \mu A$</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{CE}$ (volts)</td>
<td>$I_c$ (mA)</td>
<td>$V_{CE}$ (volts)</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

3.9 Model Graph:

Input characteristics

Output characteristics

3.10 Result

Thus the input and output characteristics of BJT in CE configuration was verified and the graph was plotted.

a) Impedance ($h_{ie}$) = $\Delta V_{BE} / \Delta I_B$, $V_{CE}$ constant.

b) Output admittance ($h_{oe}$) = $\Delta I_c / \Delta V_{EC}$, $I_B$ constant.
3.11 Prelab Questions
1. Why is base width small?
2. Why is Silicon transistor more commonly used compared to Germanium transistor?
3. What is base width modulation?
4. The junction capacitance across collector to base junction is much lower than that across base to emitter junction. Why?
5. What is the difference between diffusion capacitance and transition capacitance?
6. What is the voltage across the collector to emitter terminal when the transistor is in (i) saturation (ii) cut-off (iii) active region?

3.12 Post lab Questions
1. Design a circuit to sketch the input and output characteristics of common emitter configuration using PSPICE and compare the output with the obtained result.
2. From the above observation find forward current gain and reverse voltage gain.
3. Explain the switching action of a transistor?
4. At what region of the output characteristics, a transistor can act as an amplifier?
5. Design an NPN common emitter transistor to work as a current source. It is in which region of the transistor?
6. Based on which parameters do we choose a transistor for a particular application?
EXP 4 : JFET CHARACTERISTICS

4.1 Objective:
To study drain and transfer characteristics of a FET and measure the parameters

4.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>01</td>
<td>JFET</td>
<td>BFW10</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>02</td>
<td>Resistance</td>
<td></td>
<td>1k ohm, 10% tolerance, ½ watt rating</td>
<td>1</td>
</tr>
<tr>
<td>03</td>
<td>Regulated power supply</td>
<td></td>
<td>(0 – 30V), 2A Rating</td>
<td>1</td>
</tr>
<tr>
<td>04</td>
<td>Ammeter MC</td>
<td></td>
<td>(0-30)mA</td>
<td>1</td>
</tr>
<tr>
<td>05</td>
<td>Voltmeter MC</td>
<td></td>
<td>(0 – 30)V</td>
<td>2</td>
</tr>
<tr>
<td>06</td>
<td>Bread board and connecting wires</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

4.3 Introduction:
The field effect transistor (FET) is made of a bar of N type material called the SUBSTRATE with a P type junction (the gate) diffused into it. With a positive voltage on the drain, with respect to the source, electron current flows from source to drain through the CHANNEL. If the gate is made negative with respect to the source, an electrostatic field is created which squeezes the channel and reduces the current.
If the gate voltage is high enough the channel will be "pinched off" and the current will be zero. The FET is voltage controlled, unlike the transistor which is current controlled. This device is sometimes called the junction FET or IGFET or JFET.

If the FET is accidentally forward biased, gate current will flow and the FET will be destroyed. To avoid this, an extremely thin insulating layer of silicon oxide is placed between the gate and the channel.

The device is then known as an insulated gate FET, or IGFET or metal oxide semiconductor FET (MOSTFET) Drain characteristics are obtained between the drain to source voltage (VDS) and drain current (ID) taking gate to source voltage (VGS) as the parameter. Transfer characteristics are obtained between the gate to source voltage (VGS) and Drain current (ID) taking drain to source voltage (VDS) as parameter.

4.4 Circuit diagram:

4.5 Pin assignment of JFET (BFW10):

BFW10 – Silicon- N channel Depletion mode FET manufactured by MOTOROLA.
4.6 Characteristics of JFET:

In BFW10 JFET,

1. The transconductance $g_m$ of JFET at zero gate–source voltage is in the range of 0.1 to 10mA/V. (Since drain current is proportional to $g_m$, for more transconductance MOSFETs can be preferred).

2. Gate leakage current of JFET is in the range of 100µA to 10nA, which consumes power (whereas MOSFET has 100nA to 10pA).

3. Greater susceptibility to damage in its handling.

4.7 Precautions:

1. While doing the experiment do not exceed the ratings of the FET. This may lead to damage the FET.

2. Connect voltmeter and Ammeter in correct polarities as shown in the Circuit diagram.

3. Do not switch ON the power supply unless you have checked the Circuit connections as per the circuit diagram.

4. Make sure while selecting the Source, Drain and Gate terminals of the FET.

4.8 Tabular Column:

<table>
<thead>
<tr>
<th>Drain Characteristics</th>
<th>Transfer Characteristics</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{GS}$ =</td>
<td>$V_{GS}$ =</td>
</tr>
<tr>
<td>$V_{DS}$ (V)</td>
<td>$V_{DS}$ (V)</td>
</tr>
<tr>
<td>$I_D$ (mA)</td>
<td>$I_D$ (mA)</td>
</tr>
<tr>
<td>$V_{GS}$ (V)</td>
<td>$I_D$ (mA)</td>
</tr>
<tr>
<td>$V_{GS}$ (V)</td>
<td>$I_D$ (mA)</td>
</tr>
</tbody>
</table>
4.9 Model Graph:

**Drain Characteristics**

**Transfer Characteristics:**

4.9.1 **Graph (Instructions):**

1. Plot the drain characteristics by taking $V_{DS}$ on X-axis and $I_D$ on Y-axis at constant $V_{GS}$.
2. Plot the Transfer characteristics by taking $V_{GS}$ on X-axis and $I_D$ on Y-axis at constant $V_{DS}$.

4.10 **Calculations from Graph:**

4.10.1 **Drain Resistance (rd):**

It is given by the ratio of small change in drain to source voltage ($\Delta V_{DS}$) to the corresponding change in Drain current ($\Delta I_D$) for a constant gate to source voltage ($V_{GS}$), when the JFET is operating in pinch-off or saturation region.

4.10.2 **Trans-Conductance (gm):**

The ratio of small change in drain current ($\Delta I_D$) to the corresponding change in gate to source voltage ($\Delta V_{GS}$) for a constant $V_{DS}$ (gm = $\Delta I_D / \Delta V_{GS}$ at constant $V_{DS}$ (from transfer characteristics)). The value of gm is expressed in mhos or Siemens (s).

4.10.3 **Amplification Factor ($\mu$):**

It is given by the ratio of small change in drain to source voltage ($\Delta V_{DS}$) to the corresponding change in gate to source voltage ($\Delta V_{GS}$) for a constant drain current.

$$\mu = \frac{\Delta V_{DS}}{\Delta V_{GS}}.$$

$$\mu = \frac{\Delta V_{DS}}{\Delta I_D} \times \frac{\Delta I_D}{\Delta V_{GS}}$$

$$\mu = rd \times gm.$$
4.11 Result:
Thus the drain and transfer characteristics of a JFET was studied and verified, the following parameters were calculated

i. Drain Resistance ($r_d$) = ............

ii. Transconductance ($g_m$) = ............

iii. Amplification factor ($\mu$) = ............

4.12 Prelab Questions:

1. Why FET is called as a Unipolar transistor?
2. What are the advantages of FET over BJT?
3. State why FET is voltage controlled device?
4. JFET operates in either Enhancement mode or Depletion mode or both. Why?
5. How electron flows through P-channel JFET?

Post lab Questions:

1. Simulate using PSPICE and compare the Drain and Transfer characteristics of JFET with the obtained result.
2. Why current gain is an important parameter in BJT where as conductance is important parameter in FET?
3. Why does drain current remains physically constant above pinch off voltage?
4. What are the conditions to be satisfied for the JFET to work in pinch off or active region?
5. State the reason for non symmetrical nature of depletion region around gate to source junction.
6. Interpret transfer characteristics curve from the following drain characteristics.
EXP 5: CHARACTERISTICS OF LDR, PHOTODIODE, PHOTOTRANSISTOR

5.1 Objective:

To study and verify the characteristics of LDR, Photodiode and Phototransistor

5.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>01</td>
<td>Resistors</td>
<td></td>
<td>1KΩ,10KΩ,100KΩ, 10% tolerance,1/2 watt rating</td>
<td>1</td>
</tr>
<tr>
<td>02</td>
<td>Photodiode</td>
<td>QSD 2030F</td>
<td>1</td>
<td>1</td>
</tr>
<tr>
<td>03</td>
<td>Phototransistor</td>
<td>BPW77NA</td>
<td>1</td>
<td>1</td>
</tr>
<tr>
<td>04</td>
<td>Regulated power supply</td>
<td>(0-30V), 2A Rating</td>
<td>1</td>
<td></td>
</tr>
<tr>
<td>05</td>
<td>Ammeter</td>
<td>MC</td>
<td>(0-30)mA;(0-30)microA</td>
<td>1</td>
</tr>
<tr>
<td>06</td>
<td>Voltmeter</td>
<td>MC</td>
<td>(0-10)V</td>
<td>1</td>
</tr>
<tr>
<td>07</td>
<td>Bread board and connecting wires</td>
<td></td>
<td>1</td>
<td>1</td>
</tr>
<tr>
<td>08</td>
<td>LDR</td>
<td></td>
<td></td>
<td>1</td>
</tr>
</tbody>
</table>

5.3 Introduction

5.3.1 LDR

A photoresistor or light dependent resistor or cadmium sulfide (CdS) cell is a resistor whose resistance decreases with increasing incident light intensity. It can also be referred to as a photoconductor.

A photoresistor is made of a high resistance semiconductor. If light falling on the device is of high enough frequency, photons absorbed by the semiconductor give bound electrons enough energy to jump into the conduction band. The resulting free electron (and its hole partner) conduct electricity, thereby lowering resistance.

5.3.2 Photodiode

A silicon photodiode is a solid state light detector that consists of a shallow diffused P-N junction with connections provided to the outside world. When the top
surface is illuminated, photons of light penetrate into the silicon to a depth determined by the photon energy and are absorbed by the silicon generating electron-hole pairs. The electron-hole pairs are free to diffuse (or wander) throughout the bulk of the photodiode until they recombine.

The average time before recombination is the “minority carrier lifetime”. At the P-N junction is a region of strong electric field called the depletion region. It is formed by the voltage potential that exists at the P-N junction. Those light generated carriers that wander into contact with this field are swept across the junction.

If an external connection is made to both sides of the junction a photo induced current will flow as long as light falls upon the photodiode. In addition to the photocurrent, a voltage is produced across the diode. In effect, the photodiode functions exactly like a solar cell by generating a current and voltage when exposed to light.

5.3.3 Phototransistor:

Photo-Transistor is a bit like a Photo-Diode in the fact that it detects light waves, however photo-transistors, like transistor are designed to be like a fast switch and is used for light wave communications and as light or infrared sensors. The most common form of photo-transistor is the NPN collector and emitter transistor with no base lead. Light or photons entering the base (which is the inside of the photo-transistor) replace the base - emitter current of normal transistors.

5.4 Circuit diagram:

5.4.1 LDR

5.4.2 Photodiode
5.4.3 Phototransistor:

![Phototransistor Circuit Diagram]

5.5 Tabular Column:

5.5.1 LDR

<table>
<thead>
<tr>
<th>Distance (cm)</th>
<th>Voltage (V)</th>
<th>Current (mA)</th>
<th>Resistance (KΩ)</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
### 5.5.2 Photodiode

<table>
<thead>
<tr>
<th>Distance (cm)</th>
<th>Current (µS)</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
</tr>
</tbody>
</table>

### 5.5.3 Photo Transistor

<table>
<thead>
<tr>
<th>Distance (cm)</th>
<th>Current (µS)</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
</tr>
</tbody>
</table>
5.6 Characteristics of LDR, Photodiode, Phototransistor:
1. The dark resistance of an LDR is quite less compared with the reverse bias resistance offered by photo diodes because of which it may consume comparatively more power than its semiconductor counterparts.
2. Phototransistors made of silicon are not capable of handling voltages over 1,000 Volts.
3. Phototransistors are also more vulnerable to surges and spikes of electricity as well as electromagnetic energy.
4. Phototransistors also do not allow electrons to move as freely as other devices do, such as electron tubes.
5. The phototransistor has maximum sensitivity in the infrared (around a wavelength of 940nm), which is typical for silicon photodiodes and phototransistors.
6. Photoresistors are less light-sensitive devices than photodiodes or phototransistors: the two latter components are true semiconductor devices, while a photoresistor is a passive component and does not have a PN-junction. The photoresistivity of any photoresistor may vary widely depending on ambient temperature, making them unsuitable for applications requiring precise measurement of or sensitivity to light.
7. Photoresistors also exhibit a certain degree of latency between exposure to light and the subsequent decrease in resistance, usually around 10 milliseconds. The lag time when going from lit to dark environments is even greater, often as long as one second.

5.7 Precautions:
1. While doing the experiment do not exceed the ratings of the diode. This may lead to damage the diode.
2. Connect voltmeter and Ammeter in correct polarities as shown in the circuit diagram.
3. Do not switch ON the power supply unless you have checked the circuit connections as per the circuit diagram.
5.8 Procedure:

5.8.1 LDR:
1. Connect circuit as shown in figure 5.4.1
2. Keep light source at a distance and switch it ON, so that it falls on the LDR
3. Note down current and voltage in ammeter and voltmeter.
4. Vary the distance of the light source and note the V & I.
5. Sketch graph between R as calculated from observed V and I and distance of light source

5.8.2 Photodiode:
1. Connect circuit as shown in figure 5.4.2
2. Maintain a known distance between the bulb and photodiode say 5cm
3. Set the bulb voltage, vary the voltage of the diode in steps of 1V and note the diode current Ir.
4. Repeat above procedure for VL=4V, 6V, etc.
5. Plot the graph: Vd Vs Ir for constant VL

5.8.3 Phototransistor:
1. Connect circuit as shown in figure 5.4.3
2. Repeat the procedure as that of the photodiode.

5.9 Model Graph:

LDR

Photodiode

Phototransistor
5.10 Result:

Thus the characteristics of LDR, Photodiode, Phototransistor were studied and verified.

5.11 Prelab Questions:
1. Give the principle of operation of LDR, Photodiode and Phototransistor?
2. What is the difference between Photodiode and phototransistor?
3. Give the applications of LDR, Photodiode and Phototransistor?
4. Differentiate Direct and Indirect Semiconductor. Which is used as Optoelectronic Device? Why?
5. What is Photogeneration and Radiative Recombination?

5.12 Post lab Questions:
1. Simulate using PSPICE to get the characteristics of LDR, Photodiode and phototransistor.
2. What happens when distance is increased in case of LDR, Photodiode and phototransistor?
3. Define dark current in photodiode?
4. Can we operate photodiode in forward bias condition? Justify the answer?
5. Why we are making light to fall on collector base junction in case of phototransistor?
6. For applications requiring wavelength from 400 to 1700 nm, which material must be used to manufacture phototransistor.
6 HALF WAVE RECTIFIER

6.1 Objective:
1. To plot Output waveform of the Half Wave Rectifier.
2. To find ripple factor for Half Wave Rectifier using the formulae.
3. To find the efficiency, Vr(pp), Vdc for Half Wave Rectifier.

6.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
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</thead>
<tbody>
<tr>
<td>01</td>
<td>Transformer</td>
<td></td>
<td>6-0-6 V, 500mA, 1A Rating</td>
<td>1</td>
</tr>
<tr>
<td>02</td>
<td>Resistance</td>
<td></td>
<td>470 ohm, 10% tolerance, 1/2 watt rating</td>
<td>1</td>
</tr>
<tr>
<td>03</td>
<td>Capacitor</td>
<td></td>
<td>470µF</td>
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</tr>
<tr>
<td>04</td>
<td>Diode IN4001</td>
<td></td>
<td></td>
<td>1</td>
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<tr>
<td>05</td>
<td>Bread board and connecting wires</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

6.3 Introduction:

A device is capable of converting a sinusoidal input waveform into a unidirectional waveform with non-zero average component is called a rectifier. A practical half wave rectifier with a resistive load is shown in the circuit diagram. In positive half cycle, Diode D is forward biased and conducts. Thus the output voltage is same as the input voltage. In the negative half cycle, Diode D is reverse biased, and therefore output voltage is zero. A smoothing filter is induced between the rectifier and load in order to attenuate the ripple component. The filter is simply a capacitor connected from the rectifier output to ground. The capacitor quickly charges at the beginning of a cycle and slowly discharges through RL after the positive peak of the input voltage. The variation in the capacitor voltage due to charging and discharging is
called ripple voltage. Generally, ripple is undesirable, thus the smaller the ripple, the 
better the filtering action.

Ripple factor is a measure of effectiveness of a rectifier circuit and defined as a 
ratio of RMS value of ac component to the dc component in the rectifier output.

**Theoretical calculations for Ripple Factor:**

**Without Filter:**

\[ V_{\text{rms}} = \frac{V_m}{2} \]

\[ V_{dc} = \frac{V_m}{\pi} \]

\[ \gamma = \frac{V_{ac}}{V_{dc}} \]

\[ \text{Ripple factor (Theoretical)} \]

Where \( V_{ac} = \sqrt{(V_{rms}^2 - V_{dc}^2)} \)

\[ \gamma = \frac{V_{ac}}{V_{dc}} \] where \( V_{ac} = \sqrt{(V_{rms}^2 - V_{dc}^2)} \)

**With Filter:**

\[ r = \frac{1}{2\sqrt{3}fCR} \]

Where \( f = 50\text{Hz}, R = 1K\Omega, C = 1000\mu\text{F} \)

\[ V_{ac} = \frac{V_{r(p-p)}}{2\sqrt{3}} \]

\[ V_{dc} = V_m - \frac{V_{r(p-p)}}{2} \]

\[ \gamma = \frac{V_{ac}}{V_{dc}} \]

**Ripple Factor (practical)**

\[ \text{Percentage Regulation} = \frac{V_{NL} - V_{FL}}{V_{FL}} \times 100\% \]

\( V_{NL} \) = DC voltage at the load without connecting the load (Minimum current).

\( V_{FL} \) = DC voltage at the load with load connected.

\[ \eta = \frac{P_{DC}}{P_{AC}} \]

\( P_{AC} = V_{2\text{rms}} / R_L \)

\( P_{DC} = V_{dc} / R_L \)

The ripple factor can be lowered by increasing the value of the filter capacitor or 
increasing the load capacitance.
6.4 Circuit Diagram of Half Wave Rectifier

![Circuit Diagram of Half Wave Rectifier]

6.5 Characteristics of Half Wave Rectifier:

1. The output current in the load contains, in addition to dc component, ac components of basic frequency equal to that of the input voltage frequency. Ripple factor is high and an elaborate filtering is, therefore, required to give steady dc output.

2. The power output and, therefore, rectification efficiency is quite low. This is due to the fact that power is delivered only during one half cycle of the input alternating voltage.

3. Transformer utilization factor is low.

4. DC saturation of transformer core resulting in magnetizing current and hysteresis losses and generation of harmonics.

6.6 Precautions:

1. While doing the experiment do not exceed the ratings of the diode. This may lead to damage the diode.

2. Connect CRO using probes properly as shown in the circuit diagram.

3. Do not switch ON the power supply unless you have checked the circuit connections as per the circuit diagram.
6.7 Experiment:
1. Connections are given as per the circuit diagram without capacitor.
2. Apply AC main voltage to the primary of the transformer. Feed the rectified output voltage to the CRO and measure the time period and amplitude of the waveform.
3. Now connect the capacitor in parallel with load resistor and note down the amplitude and time period of the waveform.
4. Measure the amplitude and time period of the transformer secondary (input waveform) by connecting CRO.
5. Plot the input, output without filter and with filter waveform on a graph sheet.
6. Calculate the ripple factor.

6.8 Graph (instructions):
1. Take a graph sheet and divide it into 2 equal parts. Mark origin at the center of the graph sheet.
2. Now mark x-axis as Time and y-axis as Voltage
3. Mark the readings tabulated for Amplitude as Voltage and Time in graph sheet.

6.9 Observations:

<table>
<thead>
<tr>
<th></th>
<th>Input Waveform</th>
<th>Output Waveform (without filter)</th>
<th>Ripple Voltage (with filter)</th>
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</thead>
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<td>Amplitude</td>
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<tr>
<td>Frequency</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

6.10 Result:
The Rectified output Voltage of Half Wave Rectifier Circuit is observed and the calculated value of ripple factor is ________________
6.11 Pre Lab
1. What is the purpose of a rectifier?
2. Why filter is used in a rectifier?
3. What are the advantages of half wave rectifier?
4. Define Ripple factor and Efficiency. State the ideal values.
5. Define PIV. Give the PIV of Half wave rectifier.

6.13 Post Lab
1. Simulate Half wave rectifier with the given specifications for with and without filter using Pspice. Compare the output with the theoretical value.
2. If the input supply is 60Hz, what will be the output ripple frequency in half wave rectifier?
3. Find the ripple factor for a half wave rectifier circuit with resistor 470 Ω and capacitor 47µF.
4. Silicon diode in a half-wave rectifier has a barrier potential of 0.7V. This has the effect of reducing the peak output voltage by 0.7 V. increasing the peak output voltage by 0.7 V. reducing the peak input voltage by 0.7 V. no effect.
5. For an ideal power supply, the output voltage should be of load current and the percentage regulation should be.
7. FULL WAVE RECTIFIER

7.1 Objective:
1. To plot Output waveform of the Full Wave Rectifier.
2. To find ripple factor for Full Wave Rectifier using the formulae.
3. To find the efficiency, Vp(rect), Vdc for Full Wave Rectifier.

7.2 Hardware Required:

<table>
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<td>IN4001</td>
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<td>05</td>
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<td></td>
<td></td>
</tr>
</tbody>
</table>

7.3 Introduction:

A device is capable of converting a sinusoidal input waveform into a unidirectional waveform with non zero average component is called a rectifier. A practical half wave rectifier with a resistive load is shown in the circuit diagram. It consists of two half wave rectifiers connected to a common load. One rectifies during positive half cycle of the input and the other rectifying the negative half cycle. The transformer supplies the two diodes (D1 and D2) with sinusoidal input voltages that are equal in magnitude but opposite in phase. During input positive half cycle, diode D1 is ON and diode D2 is OFF. During negative half cycle D1 is OFF and diode D2 is ON. Peak Inverse Voltage (PIV) is the maximum voltage that has to be withstand by a diode when it is reverse biased. Peak inverse voltage for Full Wave Rectifier is $2V_m$ because the entire secondary voltage appears across the non-conducting diode.

The output of the Full Wave Rectifier contains both ac and dc components. A majority of the applications, which cannot tolerate a high value ripple, necessitates further processing of the rectified output. The undesirable ac components i.e. the ripple, can be minimized using filters.
7.3.1 Ripple Factor:
Ripple factor is defined as the ratio of the effective value of AC components to the average DC value. It is denoted by the symbol \( \gamma \).

\[
\gamma = \frac{V_{ac}}{V_{dc}}, \ (\gamma = 0.48)
\]

7.3.2 Efficiency:
The ratio of output DC power to input AC power is defined as efficiency.

\[
\eta = \frac{(V_{dc})^2}{(V_{ac})^2}
\]

\( \eta = 81\% \) (if \( R >> R_f \), then \( R_f \) can be neglected).
The maximum efficiency of a Full Wave Rectifier is 81.2%.

Percentage of Regulation:
It is a measure of the variation of DC output voltage as a function of DC output current (i.e., variation in load).

Percentage of regulation = \( \frac{(V_{NL} - V_{FL})}{V_{FL}} \times 100\% \)

\( V_{NL} = \) Voltage across load resistance, when minimum current flows through it.
\( V_{FL} = \) Voltage across load resistance, when maximum current flows through.

For an ideal Full-wave rectifier, the percentage regulation is 0 percent. The percentage of regulation is very small for a practical full wave rectifier.

Peak- Inverse - Voltage (PIV):
It is the maximum voltage that the diode has to withstand when it is reverse biased.

\( PIV = 2V_m \)

7.3.3 Transformer Utilization Factor
Transformer utilization factor (TUF), which is defined as the ratio of power delivered to the load and ac rating of the transformer secondary, So

\( TUF = \frac{dc \ power \ delivered \ to \ the \ load/\ ac \ rating \ of \ transformer \ secondary}{\text{Transformer Utilization Factor, TUF can be used to determine the rating of a transformer secondary. It is determined by considering the primary and the secondary winding separately and it gives a value of 0.693.}} \)
7.4 Theoretical Calculations:

Without filter:

\[ V_{rms} = \frac{V_m}{\sqrt{2}} \]
\[ V_{ac} = \sqrt{(V_{rms}^2 - V_{dc}^2)} \]
\[ V_{dc} = \frac{2V_m}{\pi} \]

Ripple factor (Theoretical) = \[ \sqrt{\left(\frac{V_{rms}}{V_{dc}}\right)^2 - 1} = 0.48 \]

Ripple Factor (Practical) \[ \gamma = \frac{V_{ac}}{V_{dc}} \]

With filter:

\[ \gamma = \frac{1}{4\sqrt{3}fCR} \]

Where \( f = 50\text{Hz} \), \( R = 1\text{K}\Omega \), \( C = 1000\mu\text{F} \).

\[ V_{ac} = \frac{V_{r(p-p)}}{2\sqrt{3}} \]
\[ V_{dc} = V_m - \frac{V_{r(p-p)}}{2} \]

Ripple Factor \[ \gamma = \frac{V_{ac}}{V_{dc}} \]

Percentage Regulation = \( \frac{V_{NL} - V_{FL}}{V_{FL}} \) * 100 %

\( V_{NL} \) = DC voltage at the load without connecting the load (Minimum current).
\( V_{FL} \) = DC voltage at the load with load connected.

Efficiency \[ \eta = \frac{P_{DC}}{P_{AC}} \times 100\% \]

\( P_{AC} = V_{2rms} / R_L \)
\( P_{DC} = V_{dc} / R_L \)
7.5 Circuit Diagram:

7.6 MODEL GRAPH:

7.7 Characteristics of Full Wave Rectifier:
1. The peak voltage in the full-wave rectifier is only half the peak voltage in the half-wave rectifier. This is because the secondary of the power transformer in the full-wave rectifier is center tapped; therefore, only half the source voltage goes to each diode.

2. A larger transformer for a given power output is required with two separate but identical secondary windings making this type of full wave rectifying circuit costly compared to the “Full Wave Bridge Rectifier” circuit equivalent.
7.8 Precautions:
1. While doing the experiment do not exceed the ratings of the diode. This may lead to damage the diode.
2. Connect CRO using probes properly as shown in the circuit diagram.
3. Do not switch **ON** the power supply unless you have checked the circuit connections as per the circuit diagram.

7.9 Procedure:
1. Connections are given as per the circuit diagram without capacitor.
2. Apply AC main voltage to the primary of the transformer. Feed the rectified output voltage to the CRO and measure the time period and amplitude of the waveform.
3. Now connect the capacitor in parallel with load resistor and note down the amplitude and time period of the waveform.
4. Measure the amplitude and time period of the transformer secondary(input waveform) by connecting CRO.
5. Plot the input, output without filter and with filter waveform on a graph sheet.
6. Calculate the ripple factor.

7.10 Graph (instructions)

1. Take a graph sheet and divide it into 2 equal parts. Mark origin at the center of the graph sheet.
2. Now mark x-axis as Time y-axis as Voltage
3. Mark the readings tabulated for Amplitude as Voltage and Time in graph sheet.

7.11 Observations:

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<td></td>
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<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
7.12 Result:
The Rectified output Voltage of Full Wave Rectifier Circuit is observed and the calculated value of ripple factor is _______________

7.13 Prelab Questions
1. Each diode in a centre-tapped full-wave rectifier is _____ -biased and conducts for _____ of the input cycle.
   a) Forward, 90°
   b) Reverse, 180°
   c) Forward, 180°
   d) Reverse, 90°

2. What is the VRRM (PIV rating) for the 1N4001 rectifier diode? Give the PIV of Full Wave Rectifier.


7.14 Postlab Questions
1. Simulate Full wave rectifier with the given specifications for with and without filter using Pspice. Compare the output with the theoretical value.

2. Calculate the ripple voltage of a full-wave rectifier with a 75-μF filter capacitor connected to a load drawing 40 mA.
   a. 1.20V
   b. 1.28V
   c. 1.32V
   d. 1.41V

3. The output frequency of a full-wave rectifier is _____ the input frequency

4. In the full-wave rectifier circuit,(fig 7.5) what will happen to the circuit if 1) D1 is disconnected, 2) D1’s polarity is reversed.

5. In this rectifier circuit, the output voltage is less than half of the secondary winding’s rated voltage (12 volts). Why is this?
Also, interpret whether this is a half-wave or a full-wave rectifier circuit, and explain.

6. Compare the ripple factors of half wave and full wave rectifier.
EXP 8: FULL WAVE BRIDGE RECTIFIER

8.1 Objective:

To study and verify the working of a full wave bridge rectifier with and without filter and to measure its parameters

8.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
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<td></td>
<td>connecting wires</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

8.3 Introduction:

A device is capable of converting a sinusoidal input waveform into a unidirectional waveform with non zero average component is called a rectifier. The Bridge rectifier is a circuit, which converts an ac voltage to dc voltage using both half cycles of the input ac voltage. The Bridge rectifier has four diodes connected to form a Bridge. The load resistance is connected between the other two ends of the bridge.

For the positive half cycle of the input ac voltage, diode D1 and D3 conducts whereas diodes D2 and D4 remain in the OFF state. The conducting diodes will be in series with the load resistance RL and hence the load current flows through RL. For the negative half cycle of the input ac voltage, diode D2 and D4 conducts whereas diodes D1 and D3 remain in the OFF state.

The conducting diodes will be in series with the load resistance RL and hence the load current flows through RL in the same direction as in the previous half cycle. Thus a bidirectional wave is converted into a unidirectional wave. Ripple factor is a measure of effectiveness of a rectifier circuit and defined as a ratio of RMS value of ac component to the dc component in the rectifier output.
8.4 Theoretical calculations: 8.4.1 Ripple Factor

The ripple factor for a Full Wave Rectifier is given by

\[ \gamma = \sqrt{\frac{V_{\text{rms}}}{V_{\text{dc}}}} - 1 \]

The average voltage for the DC voltage available across the load resistance is

\[ V_{\text{dc}} = 2V_m/\pi \]

The RMS value of the voltage at the load resistance is \( V_{\text{rms}} = V_m \)

Ripple factor

\[ \gamma = \sqrt{\left(\frac{V_m/2}{2V_m/\pi}\right)^2 - 1} = \sqrt{\left(\frac{\pi}{8}\right)^2 - 1} = 0.48 \]

The ripple factor can be lowered by increasing the value of the filter capacitor or increasing the load capacitance.

8.4.2 Efficiency

Efficiency, \( \eta \) is the ratio of dc output power to ac input power

\[ \eta = \frac{\text{dc output power}}{\text{ac input power}} = \frac{P_{\text{dc}}}{P_{\text{ac}}} \]

\[ \frac{V_{\text{dc}}^2}{R_L} = \left(\frac{2V_m}{\pi}\right)^2 = \frac{8}{\pi^2} = 0.812 = 81.2\% \]

The maximum efficiency of a Full Wave Rectifier is 81.2%.

8.4.3 Transformer Utilization Factor

Transformer utilization factor (TUF), which is defined as the ratio of power delivered to the load and ac rating of the transformer secondary, So

\[ \text{TUF} = \frac{\text{dc power delivered to the load}}{\text{ac rating of transformer secondary}} \]

Transformer Utilization Factor, TUF can be used to determine the rating of a transformer secondary. It is determined by considering the primary and the secondary winding separately and it gives a value of 0.812.
8.5 Circuit Diagram:

![Circuit Diagram Image]

8.6 Model Graph:

![Model Graph Image]

8.7 Precautions:
1. While doing the experiment do not exceed the ratings of the diode. This may lead to damage the diode.
2. Connect CRO using probes properly as shown in the circuit diagram.
3. Do not switch ON the power supply unless you have checked the circuit connections as per the circuit diagram.

8.8 Procedure:
1. Connections are given as per the circuit diagram without capacitor.
2. Apply AC main voltage to the primary of the transformer. Feed the rectified output voltage to the CRO and measure the time period and amplitude of the waveform.
3. Now connect the capacitor in parallel with load resistor and note down the amplitude and time period of the waveform.
4. Measure the amplitude and time period of the transformer secondary (input waveform) by connecting CRO.
5. Plot the input, output without filter and with filter waveform on a graph sheet.
6. Calculate the ripple factor.

8.9 Formulae:

**Peak to Peak Ripple Voltage**, \( V_{r(pp)} = \frac{V_{p(rect)}}{2fRLC} \)

Where \( V_{p(rect)} \) - Unfiltered Peak Rectified Voltage

**Peak rectified voltage**, \( V_{dc} = (1 - \frac{1}{4fRLC})V_{p(rect)} \)

Ripple Factor = \( V_{r(pp)}/V_{dc} \)

8.10 Observations:

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<th>Ripple Voltage (with filter)</th>
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</tbody>
</table>

8.11 Result:

The rectified output voltage of full wave bridge rectifier circuit is observed and the calculated value of **ripple factor** is ______________

8.12 Prelab Questions:

1. What is the PIV of a diode full wave bridge rectifier circuit?

2. A bridge rectifier is preferable to a full-wave rectifier using center-tap transformer as
   
   (a) It uses four diodes
   (b) Its transformer does not require center-tap
   (c) It requires much smaller transformer for the same output
   (d) All of these

3. In a full-wave bridge rectifier, the current in each diode flows for
   
   (a) Complete cycle of the input signal
   (b) Half-cycle of the input signal
   (c) Less than half-cycle of the input signal
   (d) More than half-cycle of the input signal
4. What is the purpose of a filter in dc power supply?
5. What is TUF? Give the TUF of half wave, full wave-center tapped and bridge rectifier.

8.13 Post lab Questions:
1. Simulate Fullwave Bridge rectifier with the given specifications for with and without filter using PSPICE. Compare the output with the theoretical value
2. When a 50Hz ac signal is fed to a rectifier, the ripple frequency of the output voltage waveform for full bridge rectifier is
   (a) 25 Hz    (b) 50 Hz
   (c) 100 Hz   (c)150 Hz

3. Trace the current through this rectifier circuit at a moment in time when the AC source’s polarity is positive on right and negative on left as shown. Be sure to designate the convention you use for current direction (conventional or electron flow):

   ![Circuit Diagram]

4. For the figure shown below. Determine (a) the DC output voltage, (b) DC load current, (c) the RMS value of the load current, (d) the DC power, (e) the AC power, (f) efficiency of rectifier, (g) peak inverse voltage of each diode, and (h) output frequency. Assume all diodes are ideal.
9. SERIES VOLTAGE REGULATOR

9.1 Objective:
1. To design a series voltage regulator
2. To find load regulation
3. To find line regulation

9.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>Power transistor</td>
<td>2N3055</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>2</td>
<td>Transistor</td>
<td>BC147</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>3</td>
<td>Zener diode</td>
<td>1Z6.2</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>4</td>
<td>Resistors</td>
<td>947Ω, 2.48KΩ, 2.2kΩ, 2.75KΩ, 49.6Ω, 10% tolerance, ½ watt</td>
<td>1</td>
<td></td>
</tr>
<tr>
<td>5</td>
<td>Voltmeter</td>
<td>MC</td>
<td>(0 – 30)V</td>
<td>1</td>
</tr>
<tr>
<td>6</td>
<td>Bread board &amp; wires</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>7</td>
<td>Decade Resistance Box</td>
<td>50Ω</td>
<td></td>
<td>1</td>
</tr>
</tbody>
</table>

9.3 Introduction:

The term regulation is the ability of the power supply source to maintain a constant output voltage in spite of line voltage fluctuations and changes in load current. The factors of poor regulation are

1. The line voltage changes which causes a dc output change and the ripple content of the dc input due to inadequate filtering.
2. The load current changes which causes a variable internal drop due to the internal resistance of the regulator and the consequent change in the output voltage and
3. The temperature coefficient of the device parameters which results in a change of the output voltage.
Voltage regulators can be classified by the method of achieving regulation as linear regulators and switching regulators. They are also classified by the way they are connected to the load as series regulators and shunt regulators. Standard regulator contains three basic elements namely a precision voltage reference, an error amplifier and a power control element.

In this circuit the transistor Q2 Functions both as a voltage comparator and dc amplifier. Any increase in the output voltage \( V_o \) either due to the input-voltage variation or change of load results in increase of \( V_{BE} \) of the transistor Q2. Hence the collector current \( I_C \) increase. Due to this the total current following through \( R_3 \) increases. Hence the collector voltage of Q2 decreases.

Since the base of Q1 is tied to the collector of T2, the base voltage of Q1 with respect to ground decreases thereby decreasing the forward bias of the emitter junction of Q2. Hence the collector emitter voltage of Q1 has to increase in order to maintain the same emitter current. If the change in \( V_{CE} \), of Q1 can be made equal to \( V_i \) then the output voltage will remain constant. Since \( V_{CBI}=V_{CEI} \). We can assume that if \( V_i \) dropped across \( R_3 \), then the output voltage will remain constant.

9.3.1 Line Regulation:

Line regulation is a measure of the ability of the power supply to maintain its output voltage given changes in the input line voltage. Line regulation is expressed as percent of change in the output voltage relative to the change in the input line voltage.

\[
\text{Line regulation} = \frac{\text{output voltage at High line input voltage} - \text{output voltage at low line input voltage}}{\text{High line input voltage} - \text{low line input voltage}} \times 100
\]

9.3.2 Load Regulation

Load regulation is a measure of the ability of an output channel to remain constant given changes in the load. Depending on the control mode enabled on the output channel, the load regulation specification can be expressed in one of two ways In constant voltage mode, variations in the load result in changes in the output current. This variation is expressed as a percentage of range per amp of output load and is synonymous with a series resistance. In constant voltage mode, the load regulation specification defines how close the series resistance of the output is to 0 ohms - the series resistance of an ideal voltage source.
In constant current mode, variations in the load result in changes to the current through the load. This variation is expressed as a percentage of range change in current per volt of change in the output voltage and is synonymous with a resistance in parallel with the output channel terminals. In constant current mode, the load regulation specification defines how close the output shunt resistance is to infinity—the parallel resistance of an ideal current. In fact, when load regulation is specified in constant current mode, parallel resistance is expressed as $1/\text{load regulation}$.

Load Regulation can be defined as a percentage by the equation:

\[
\text{Percent of regulation} = \frac{(E_{nL} - E_{fL})}{E_{fL}} \times 100
\]

Where:

- **FullLoad** ($E_{fL}$) is the load that draws the greatest current (is the lowest specified load resistance - never short circuit)
- **MinimumLoad** ($E_{nL}$) is the load that draws the least current (is the highest specified load resistance - possibly open circuit for some types of linear supplies, usually limited by pass transistor minimum bias levels)
- **NominalLoad** ($E_{fL}$) is the typical specified operating load

### 9.4 Circuit Diagram - Series Voltage Regulator

![Circuit Diagram]

**9.4.1 Design Specifications Series pass Transistor 2N3055:**

- $h_{fe} = 20-70$
- $I_{\text{max}} = 15$ amperes
- $V_{cc} = 70V$
- BC 170
\[ I_e = 2 \text{ mA} \]
\[ h_{fe} = 125 - 500 \]

**ASSUMPTIONS**

\[ V_1 = 12.4 \text{ V} \]
\[ = 250 \text{ mA} \]
\[ = 2.5 \text{ mA} \]
\[ = 10 \text{ mA} \]
\[ \beta_1 = 28 \]
\[ \beta_2 = 188 \]

**DESIGN**

\[ \frac{V_L}{2} = \frac{12.4}{2} = 6.2 \text{ V} \]
\[ \frac{V_L}{I_L} = \frac{12.4}{250 \times 10^{-3}} = 49.6 \Omega \]
\[ 0.01 \times I_L = \frac{12.4}{250 \text{ mA}} \]
\[ \frac{V_L - V_Z}{I_D} = \frac{12.4 - 6.2}{2.5 \times 10^{-3}} = 2.48 \text{ K} \Omega \]
\[ R_1 = \frac{V_L - (V_{BE2} + V_Z)}{I_1} = \frac{(12.4 - (0.7 + 6.2))}{2.5 \times 10^{-3}} = 2.2 \text{ K} \Omega \]
\[ V_{R2} = V_{BE2} + V_Z \times \left( \frac{R_2}{R_1 + R_2} \right) \]
\[ 0.7 + 6.2 = 12.4 \times \left( \frac{R_2}{(2.2 \times 10^{-3} + R_2)} \right) \]
\[ R_2 = 2.75 \text{ K} \Omega \]
\[ I_2 = \frac{(V_2 + V_{BE2})}{R_2} = \frac{6.9}{2.75 \times 10^3} = 2.5 \text{ mA} \]
\[ I_{E1} = \frac{(I_D + I_1 + I_L)}{2.5 + 2.5 + 250} \text{ mA} = 255 \text{ mA} \]
\[ I_{B1} = \frac{I_{E1}}{\beta_1} = \frac{255}{28} = 9.107 \text{ mA} \]
\[ I_3 = I_{B1} + I_{C2} = 9.107 \text{ mA} = 19.107 \text{ mA} \]
\[ R_3 = \frac{[V_{INMX} - (V_{BE1} + V_2)]}{I_3} = \frac{25 - (0.7 \times 6.2)}{19.107 \times 10^{-3}} = 947 \Omega \]

**9.5 Characteristics of Series Voltage Regulator:**

This series voltage regulator is suitable only for low output voltages because of the following reasons:

1. With the increase in room temperature, the values of Vbe and Vzener tend to decrease. Thus the output voltage cannot be maintained a constant. This will
further increase the transistor base emitter voltage and thus the load.
2. There is no option to change the output voltage in the circuit.
3. Due to small amplification process provided by only one transistor (BC147), the circuit cannot provide good regulation at high currents.
4. The power dissipation of a pass transistor is large because it is equal to $V_{cc}I_c$ and almost all variation appears at $V_{ce}$ and the load current is approximately equal to collector current. Thus for heavy load currents pass transistor has to dissipate a lot of power and, therefore, circuit becomes hot. So some heat sink is required.

9.6 Procedure:
Connect the circuit as per the circuit diagram.
1. For load regulation characteristics, keep the input voltage constant, find $V_L$ for different values of $R_L$. Plot the graph by taking $R_L$ in the axis and $V_L$ in the Y axis.
2. For line regulation characteristics, keep $R_L$ constant and for different values of input $V_{in}$ find $V_L$. Plot the graph by taking $V_{in}$ in x axis and $V_L$ in the y axis

9.7 Tabulation
9.7.1 Line regulation $RL = \text{________} (\Omega)$

<table>
<thead>
<tr>
<th>S. No</th>
<th>$V_i$ (V)</th>
<th>$V_o$ (V)</th>
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</thead>
<tbody>
<tr>
<td>1.</td>
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<tr>
<td>12.</td>
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</tbody>
</table>
9.7.2 Load regulation \( V_i = \text{---------} \ (V) \)

<table>
<thead>
<tr>
<th>S.No</th>
<th>( R_L ) (Ω)</th>
<th>( V_o ) (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.</td>
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<td>6.</td>
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</tbody>
</table>

9.8 Model Graph

![Model Graph]

LOAD REGULATION  
LINE REGULATION

9.9 Result:

The series voltage regulator was designed and constructed and the characteristics were plotted.
1. The regulated output voltage was found to be \(-------------\) V
2. Line regulation was found to be \(-------------\)
3. Load regulation was found to be \(-------------\)

9.10 Prelab Question:
1. What are the three basic elements inside a standard voltage regulator?
2. What device is used as a control element? Why?

3. What are the performance measures of the regulator?

4. What is line regulation and Load regulation What is the efficiency of series voltage regulator

9.11 Post Lab Question:
1. Design series voltage Regulator in PSPICE and compare with obtaind line and load regulation curves.

2. With reference to the above circuit (fig 9.4), What will be the output voltage if reference voltage was short circuited?

3. The 7812 regulator IC provides ________.
   a) 5V
   b) -5V
   c) 12V
   d) -12V

4. what will happen if potential divider was open circuited

5. what is the role of resistor R1 and R2 in the circuit
10.SHUNT VOLTAGE REGULATOR

10.1 Objective:
1. To design a shunt voltage regulator
2. To find load regulation
3. To find line regulation

10.2 Hardware Required:

<table>
<thead>
<tr>
<th>S.No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>Regulated power supply</td>
<td>MC</td>
<td>(0-30 V), 2 A rating</td>
<td>1</td>
</tr>
<tr>
<td>2</td>
<td>Resistors</td>
<td></td>
<td>1K Ω, 10% tolerance, ½ watt</td>
<td>1</td>
</tr>
<tr>
<td>3</td>
<td>Zener diode</td>
<td>1z 5.1</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>4</td>
<td>Voltmeter</td>
<td></td>
<td>(0-30)V</td>
<td>1</td>
</tr>
<tr>
<td>5</td>
<td>Breadboard &amp; wires</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>6</td>
<td>Decade Resistance Box</td>
<td>1</td>
<td>10K Ω</td>
<td>1</td>
</tr>
</tbody>
</table>

10.3 Introduction:

The function of a voltage regulator is to provide a stable dc voltage to electronic circuits and capable of providing substantial output current. Since the element or component used for voltage regulation is connected across the load, it is called as shunt voltage regulator. There are two types of shunt voltage regulator:

1. Zener diode shunt voltage regulator
2. Transistor shunt voltage regulator

A zener diode is connected in parallel with the load; a resistance (R2) is connected in series with the zener to limit the current in the circuit. Hence the resistance is called as series current limiting resistor. The output voltage (V_o) is taken across the load resistance (R1). Since the reverse bias characteristics of zener diode are used in voltage regulation, the input voltage is always maintained greater than zener voltage (V_z).

10.3.1 Line Regulation:

Line regulation is a measure of the ability of the power supply to maintain its
output voltage given changes in the input line voltage. Line regulation is expressed as percent of change in the output voltage relative to the change in the input line voltage.

10.3.2 Load Regulation

Load regulation is a measure of the ability of an output channel to remain constant given changes in the load. Depending on the control mode enabled on the output channel, the load regulation specification can be expressed in one of two ways:

In constant voltage mode, variations in the load result in changes in the output current. This variation is expressed as a percentage of range per amp of output load and is synonymous with a series resistance. In constant voltage mode, the load regulation specification defines how close the series resistance of the output is to 0 ohms - the series resistance of an ideal voltage source.

In constant current mode, variations in the load result in changes to the current through the load. This variation is expressed as a percentage of range change in current per volt of change in the output voltage and is synonymous with a resistance in parallel with the output channel terminals. In constant current mode, the load regulation specification defines how close the output shunt resistance is to infinity—the parallel resistance of an ideal current. In fact, when load regulation is specified in constant current mode, parallel resistance is expressed as 1/load regulation.

Load Regulation can be defined as a percentage by the equation:

\[
\text{Percent of regulation} = \left(\frac{E_{nL} - E_{fL}}{E_{fL}}\right) \times 100
\]

Where:

- FullLoad \((E_{fL})\) is the load that draws the greatest current (is the lowest specified load resistance - never short circuit)
- MinimumLoad \((E_{nL})\) is the load that draws the least current (is the highest specified load resistance - possibly open circuit for some types of linear supplies, usually limited by pass transistor minimum bias levels)
- NominalLoad \((E_{fL})\) is the typical specified operating load \(\Omega\)

10.4 Circuit Diagram – Shunt Voltage Regulator
10.5 Design

Let $I_Z \text{ max} = 10 \text{ mA}$, $V_Z = V_L = 5.1 \text{ V}$ Load current $I_L = 50 \text{ mA}$.

Therefore $R_L = \frac{V_L}{I_L} = \frac{5.1 \text{ V}}{50 \times 10^{-3} \text{ A}} = 120 \Omega$ $R_L = 120 \Omega$

$R_L$ should be greater than or equal to $102 \Omega$ $I_1 = I_Z + I_L$

$= 10 \text{ mA} + 50 \text{ mA} I_1 = 60 \text{ mA}$

$R_s = \frac{(V_i - V_Z)}{I_1} = \frac{(7-5.1)}{(60 \times 10^{-3})} = 31.66 \Omega$

$R_s = 31.66 \Omega$

10.6 Characteristics of Shunt Voltage Regulator:
The series resistor causes a huge amount of power loss.
1. The circuit may have problems regarding over voltage mishaps.

10.7. Procedure:

10.7.1 Line regulation
1. Connections are made as per as the circuit diagram.

2. The load resistance $(R_L)$ is kept constant and input voltage is varied and the corresponding output voltage $(V_o)$ are noted.

3. A graph is drawn by taking input voltage $(V_i)$ in x axiz and output voltage $(V_o)$ in y axis.

10.7.2 Load regulation
1. The same circuit is used for finding load regulation. In the case, the input voltage $(V_i)$ is kept constant.

2. The load resistance $R_L$ is varied and the corresponding output voltage are noted.

3. A graph is plotted by having $R_L$ in x axis and $V_o$ in y axis.
10.8 Tabulation

10.8.1 Line regulation

\[ RL = \frac{V_i}{V_o} \quad (\Omega) \]

<table>
<thead>
<tr>
<th>S. No</th>
<th>( V_i ) (V)</th>
<th>( V_o ) (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.</td>
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<td>12.</td>
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</tbody>
</table>

10.8.2 Load regulation

\[ V_i = \frac{RL}{R} \quad (V) \]

<table>
<thead>
<tr>
<th>S. No</th>
<th>( RL ) (( \Omega ))</th>
<th>( V_o ) (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.</td>
<td></td>
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<td>2.</td>
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<td>5.</td>
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<tr>
<td>6.</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

10.9 Model Graph

\[ V_{in} = \text{Constant} \]
10.10 Result
The shunt voltage regulator was designed and constructed and the characteristics were plotted.
1. The regulated output voltage was found to be ____________.
2. Line regulation was found to be ________________
3. Load regulation was found to be ________________

10.11 Pre Lab Question:
1. List the difference between Series and Shunt Voltage Regulator
2. Give the application of shunt regulator
3. In the circuit of shunt voltage regulator which element is considered control element and explain its function.

10.12 Post Lab Questions
1. Design Shunt Voltage regulator in PSPICE and analyse the circuit.
2. What will be the output voltage if Zener diode was short circuited?
3. What will be the output voltage if reference voltage was open circuited?
4. What is the role of resistor R1 and R2 in the circuit?
5. The transistor shunt regulator shown in figure has a regulated output voltage of 10 volts, when input varies from 20 volts to 30 volts. The relevant parameters for the zener diode and the transistor are: \( V_Z = 9.5 \) volts, \( V_{BE} = 0.3 \) volts, \( \beta = 99 \). Neglect the current through Rb. Then the maximum power dissipated in the zener diode (\( P_Z \)) and the transistor (\( P_T \)) are

\[
\begin{align*}
(a) & \quad P_Z = 75 \text{mW}, \quad P_T = 7.9 \text{W} \\
(b) & \quad P_Z = 85 \text{mW}, \quad P_T = 8.9 \text{W} \\
(c) & \quad P_Z = 95 \text{mW}, \quad P_T = 9.9 \text{W} \\
(d) & \quad P_Z = 115 \text{mW}, \quad P_T = 11.9 \text{W}
\end{align*}
\]
11 V-I CHARACTERISTICS OF LED

11.1 Objective:

To study and verify the V-I Characteristics of LED

11.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.</td>
<td>Regulated power supply</td>
<td>(0 -5) V</td>
<td>1</td>
</tr>
<tr>
<td>2.</td>
<td>Resistors</td>
<td>330Ω, 10% tolerance, ½ watt</td>
<td>1</td>
</tr>
<tr>
<td>3.</td>
<td>LED</td>
<td>Red, Green, Yellow colours; 3mm size</td>
<td>1</td>
</tr>
<tr>
<td>4.</td>
<td>Voltmeter</td>
<td>(0 – 30)V</td>
<td>1</td>
</tr>
<tr>
<td>5.</td>
<td>Ammeter</td>
<td>(0 – 100) mA</td>
<td>1</td>
</tr>
<tr>
<td>6.</td>
<td>Bread board and connecting wires</td>
<td></td>
<td>1</td>
</tr>
</tbody>
</table>

11.3 Introduction:

LEDs emit light when an electric current passes through them. LED is connected in the circuit as shown in figure. LED operates only in forward biased condition. Under forward bias condition the anode is connected to the positive terminal and the cathode is connected to the negative terminal of the battery. It is like a normal pn junction diode except the basic semiconductor material is GaAs or InP which is responsible for the color of the light.

When it is forward biased the holes moves from p to n and electrons flow from n to p. In the junction the carriers recombine with each other and released the energy in the form of light. Thus LED emits light under forward biased condition. Under reverse biased condition, there is no recombination due to majority carriers, so there is no emission of light.

11.3.1 Connecting and soldering

LEDs must be connected the correct way round, the diagram may be labeled a or+ for anode and k or - for cathode (yes, it really is k, not c, for cathode!). The cathode is the short lead and there may be a slight flat on the body of round LEDs.

If you can see inside the LED the cathode is the larger electrode (but this is not an official identification method). LEDs can be damaged by heat when soldering, but the risk is small unless you are very slow. No special precautions are needed for soldering most LEDs.
11.3.2 Testing an LED

Never connect an LED directly to a battery or power supply! It will be destroyed almost instantly because too much current will pass through and burn it out. LEDs must have a resistor in series to limit the current to a safe value, for quick testing purposes a 1kΩ resistor is suitable for most LEDs if your supply voltage is 12V or less. Remember to connect the LED the correct way round!

11.3.3 Colours of LEDs

LEDs are available in red, orange, amber, yellow, green, blue and white. Blue and white LEDs are much more expensive than the other colours. The colour of an LED is determined by the semiconductor material, not by the colouring of the 'package' (the plastic body). LEDs of all colours are available in uncoloured packages which may be diffused (milky) or clear (often described as 'water clear'). The coloured packages are also available as diffused (the standard type) or transparent. As well as a variety of colours, sizes and shapes, LEDs also vary in their viewing angle. This tells you how much the beam of light spreads out. Standard LEDs have a viewing angle of 60° but others have a narrow beam of 30° or less.

11.3.4 Calculating an LED resistor value

An LED must have a resistor connected in series to limit the current through the LED, otherwise it will burn out almost instantly. The resistor value, R is given by:

\[ R = \frac{(V_S - V_L)}{I} \]

\[ V_S = \text{supply voltage} \]

\[ V_L = \text{LED voltage} \text{ (usually 2V, but 4V for blue and white LEDs)} \]

\[ I = \text{LED current (e.g. 20mA), this must be less than the maximum permitted.} \]
If the calculated value is not available choose the nearest standard resistor value which is greater, so that the current will be a little less than you chose. In fact you may wish to choose a greater resistor value to reduce the current (to increase battery life for example) but this will make the LED less bright.

For example If the supply voltage $V_S = 9V$, and you have a red LED ($V_L = 2V$), requiring a current $I = 20mA = 0.020A$, $R = (9V - 2V) / 0.02A = 350\Omega$, so choose $390\Omega$ (the nearest standard value which is greater).

11.3.5 Connecting LEDs in series

If you wish to have several LEDs on at the same time it may be possible to connect them in series. This prolongs battery life by lighting several LEDs with the same current as just one LED.

All the LEDs connected in series pass the same current so it is best if they are all the same type. The power supply must have sufficient voltage to provide about $2V$ for each LED ($4V$ for blue and white) plus at least another $2V$ for the resistor. To work out a value for the resistor you must add up all the LED voltages and use this for $V_L$. 
For Example a red, a yellow and a green LED in series need a supply voltage of at least $3 \times 2V + 2V = 8V$, so a 9V battery would be ideal.

$VL = 2V + 2V + 2V = 6V$ (the three LED voltages added up).

If the supply voltage $Vs$ is 9V and the current $I$ must be $15mA = 0.015A$, Resistor $R = (Vs - VL) / I = (9 - 6) / 0.015 = 3 / 0.015 = 200\,\Omega$, so choose $R = 220\,\Omega$ (the nearest standard value which is greater).

Avoid connecting LEDs in parallel. Connecting several LEDs in parallel with just one resistor shared between them is generally not a good idea. If the LEDs require slightly different voltages only the lowest voltage LED will light and it may be destroyed by the larger current flowing through it. Although identical LEDs can be successfully connected in parallel with one resistor this rarely offers any useful benefit because resistors are very cheap and the current used is the same as connecting the LEDs individually.

11.3.6 Advantages of LED:
1. Less complex circuitry
2. Can be fabricated less expensively with high yield

11.3.7 Desired characteristics:
1. Hard radiation
2. Fast emission response time
3. High quantum efficiency

11.3.8 Basic LED configuration:
1. Surface emitter
2. Edge emitter
11.4 Circuit diagram: Forward bias

![Circuit Diagram](image)

11.5 Procedure:
1. Give the connection as per the circuit diagram.
2. Vary the input voltages at the RPS and note down the corresponding current for the voltages.
3. Repeat the procedure for reverse bias condition and tabulate the corresponding voltages and currents.
4. Plot the graph between voltage and current for forward bias and reverse bias.

11.6 Tabular column:

<table>
<thead>
<tr>
<th>LED Colour: Red</th>
<th>LED Colour: Green</th>
<th>LED Colour: Yellow</th>
</tr>
</thead>
<tbody>
<tr>
<td>S. No</td>
<td>Voltage(V)</td>
<td>Current(mA)</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
1.7 Model Graph:

![Model Graph Image]

11.8 Result:

Thus the VI characteristics of LED were studied.

11.9 Pre Lab questions:

1. Differentiate LED from normal PN junction diode?
2. Define wavelength.
3. What happens when LEDs connected in series and parallel?
4. What are the advantages of LED over laser diode?
5. What are the desired characteristics of LED?

11.10 Post Lab questions:

1. Simulate using PSPICE the characteristics of Red, Green and Yellow LED’s.
2. Explain the operation of LED under forward bias and reverse bias condition?
3. Why light is not emitted under reverse bias condition?
4. Why is it important to control the current through an LED?
5. Can LEDs be dimmed? Does dimming LEDs cause color shifts?
EXP 12: COMMON COLLECTOR CONFIGURATION USING PSPICE

12.1 Objective:
To study the input and output characteristics of a transistor in common collector configuration and to determine its h-parameters.

12.2 Hardware Required:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Type</th>
<th>Range</th>
<th>Quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>01</td>
<td>Transistor</td>
<td>BC147</td>
<td></td>
<td>1</td>
</tr>
<tr>
<td>02</td>
<td>Resistance</td>
<td></td>
<td>68 k, 1k ohm</td>
<td>1</td>
</tr>
<tr>
<td>03</td>
<td>Regulated power supply</td>
<td></td>
<td>(0 – 30V)</td>
<td>2</td>
</tr>
<tr>
<td>04</td>
<td>Ammeter</td>
<td>mC</td>
<td>(1-10)mA, (0-500)μA</td>
<td>1</td>
</tr>
<tr>
<td>05</td>
<td>Voltmeter</td>
<td>mC</td>
<td>(0 – 1)V, (0 – 30)V</td>
<td>1</td>
</tr>
<tr>
<td>06</td>
<td>Bread board and connecting</td>
<td></td>
<td></td>
<td>1</td>
</tr>
<tr>
<td></td>
<td>wires</td>
<td></td>
<td></td>
<td>1</td>
</tr>
</tbody>
</table>

12.3 Introduction:
Bipolar junction transistor (BJT) is a 3 terminal (emitter, base, collector) semiconductor device. There are two types of transistors namely NPN and PNP. It consists of two P-N junctions namely emitter junction and collector junction.
In Common collector configuration the input is applied between base and collector terminals and the output is taken from collector and emitter. Here collector is common to both input and output and hence the name common collector configuration.
Input characteristics are obtained between the input current and input voltage taking output voltage as parameter. It is plotted between $V_{BC}$ and $I_B$ at constant $V_{CE}$ in CC configuration.
Output characteristics are obtained between the output voltage and output current taking input current as parameter. It is plotted between $V_{CE}$ and $I_E$ at constant $I_B$ in CC configuration.

12.4 Pin Assignment:
12.5 Circuit diagram:

12.6 Schematic Diagram

12.6.1 Input Characteristics

12.6.2 Output Characteristics
12.7 Precautions:
1. While doing the experiment do not exceed the ratings of the transistor. This may lead to damage the transistor.
2. Connect voltmeter and Ammeter in correct polarities as shown in the circuit diagram.
3. Do not switch ON the power supply unless you have checked the circuit connections as per the circuit diagram.
4. Make sure while selecting the emitter, base and collector terminals of the transistor.

12.8 Procedure:
12.8.1 Input Characteristics:
1. Connect the transistor in CC configuration as per circuit diagram 2. Keep output voltage $V_{CE} = 0V$ by varying $V_{EE}$.
3. Varying $V_{BB}$ gradually, note down both base current $I_B$ and base - collector voltage ($V_{BC}$). 4. Repeat above procedure (step 3) for various values of $V_{CE}$

12.8.2 Output Characteristics:
1. Make the connections as per circuit diagram.
2. By varying $V_{BB}$ keep the base current $I_B = 20\mu A$.
3. Varying $V_{CC}$ gradually, note down the readings of emitter-current ($I_E$) and collector- Emitter voltage ($V_{CE}$).
4. Repeat above procedure (step 3) for different values of $I_E$

12.9 Model Graph:
12.9.1 Input characteristics 12.9.2 Output Characteristics
12.10 Result:
Thus the input and output characteristics of BJT in CC configuration was verified and the graph was plotted.

i. Input impedance($h_{ic}$) = $\frac{\Delta V_{BC}}{\Delta I_B} =$ ________________

ii. Forward current gain($h_{fe}$) = $\frac{\Delta I_E}{\Delta I_B} =$ ______________________

iii. Output admittance($h_{oc}$) = $\frac{\Delta I_E}{\Delta V_{EC}} =$ __________________________

iv. Reverse voltage gain($h_{re}$) = $\frac{\Delta V_{BC}}{\Delta V_{EC}} =$ __________________________

12.11 Pre lab Questions
1. Why CC Configuration is called emitter follower?
2. Can we use CC configuration as an amplifier?
3. What is the need for analyzing the transistor circuits using different parameters?
4. What is the significance of hybrid model of a transistor?
5. Is there any phase shift between input and output in CC configuration?

12.12 Post lab Questions:
1. What are the applications of CC configuration?
2. Compare the voltage gain and input and output impedances of CE and CC configurations. BJT is a current controlled device. Justify.
13. CHARACTERISTICS OF METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS (MOSFETS) USING PSPICE

13.1 Objective:
To perform drain characteristics and transfer characteristics of MOSFET using Pspice Capture Lite Software.

13.2. Theory:
In a MOSFET, current flows from the drain terminal to the source terminal through a semiconductor channel. The resistance of the channel, and therefore its ability to conduct current, is controlled by a voltage applied to a third terminal denoted as the gate. MOSFETs can be either an n-channel type or a p-channel type. In an n-channel MOSFET a positive voltage is applied to the drain terminal for operation while in a p-channel MOSFET a negative voltage is applied to the drain terminal for operation. An n-channel and p-channel type MOSFET may be one of two modes; enhancement mode or depletion mode. The enhancement mode MOSFET is normally “off” (in cutoff and conducting no current) when no voltage is applied to the gate and is “on” (in saturation and conducting current) when a voltage greater than the gate-to-source threshold is applied to the gate. The depletion mode MOSFET is normally “on” (in saturation and conducting current) when no voltage is applied to the gate and is “off” (in cutoff and not conducting current) when a voltage more negative than the gate-to-source threshold is applied to the gate.

(a) n-channel MOSFET

(b) p-channel MOSFET
13.2.1 Transfer Characteristics:

In most MOSFET applications, an input signal is the gate voltage $V_G$ and the output is the drain current $I_D$. The ability of MOSFET to amplify the signal is given by the output/input ratio: the transconductance, $g_m = \frac{dI_D}{dV_{GS}}$ with $V_{DS}$ constant

13.2.2 Drain Characteristics:

MOSFET operates in three operation mode, Cut-off when $V_{GS} < V_{th}$, Linear mode when $V_{GS} > V_{th}$ and $V_{DS} < (V_{GS} - V_{th})$ and Saturation when $V_{GS} > V_{th}$ and $V_{DS} \geq (V_{GS} - V_{th})$. Pinch off occurs when $V_{DS} = V_{Sat} = V_{GS} - V_{th}$. The drain resistance, $R_d = \frac{dV_{DS}}{dI_D}$ with $V_{GS}$ constant

13.3 Circuit Diagram:

![Circuit Diagram](image)

13.4 Handling Precautions:

1. When handling power MOS FETs, the man should be ground. And Power MOS FETs, should be handled by the package, not by the leads.
2. When handling or installing Power MOS FETs into circuits, use metal plates that it grounded on Work Stations.
3. When testing Power MOS FETs, Test Circuit (Curve tracer, etc.) should be grounded.
4. When using soldering irons, soldering irons should be grounded. (It’s better to use battery operated soldering irons.)
5. When shipping in circuit boards, they should be placed in antistatic bags, unless the gate and the source are connected by resistors or inductors.
6. Power MOS FETs should be placed not in plastic cases or bags, but in antistatic bags, conductive foam, or aluminum foil.

13.5 Model Graph:

13.5.1 Transfer Characteristics: 13.5.2 Drain Characteristics:

![Graphs showing transfer characteristics and drain characteristics of MOSFETs.](image)

13.6 Result:
The drain Characteristics and Transfer Characteristics of MOSFET was simulated using Pspice, the transconductance = _______ and drain resistance = ________ was found.

13.7 PreLab Questions:
1. With the E-MOSFET, when gate input voltage is zero, what is the drain current?
2. When is a vertical channel E-MOSFET used?
3. Compare the input impedance of MOSFET with that of BJT and FET.
4. In MOSFET devices the N-channel type is better the P-channel type. How?

13.8 Post lab:
1. In a MOSFET, the polarity of the inversion layer is the same as that of _______.
2. What is the difference between depletion MOSFET and JFET.

Input impedance of MOSFET is
3. What are the three regions of operation in MOSFET?

4. Interpret transfer characteristics from the given drain characteristics for MOSFET.
14.1 OBJECTIVE:

To study and verify the physical characteristics of the given thermistor and calculate the resistance of the thermistor and the temperature coefficient using the given formula for different temperatures.

14.2 HARDWARE REQUIRED:

<table>
<thead>
<tr>
<th>S. No</th>
<th>Apparatus</th>
<th>Quantity</th>
<th>Type</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.</td>
<td>Thermistor</td>
<td>1</td>
<td></td>
</tr>
<tr>
<td>2.</td>
<td>Thermometer</td>
<td>1</td>
<td></td>
</tr>
<tr>
<td>3.</td>
<td>Multimeter</td>
<td>1</td>
<td>Digital</td>
</tr>
<tr>
<td>4.</td>
<td>Heater</td>
<td>1</td>
<td></td>
</tr>
<tr>
<td>5.</td>
<td>Connecting wires</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

14.3 INTRODUCTION:

A thermistor is a type of resistor whose resistance varies with temperature. The word thermistor is a combination of words “thermal” and “resistor”. A thermistor is a temperature-sensing element composed of sintered semiconductor material which exhibits a large change in resistance proportional to a small change in temperature.

Thermistors are widely used as inrush current limiters, temperature sensors, self-resetting over current protectors, and self-regulating heating elements. Assuming, as a first-order approximation, that the relationship between resistance and temperature is linear, then:

\[ R = k T \]

Where \( R \) = change in resistance.
\( T \) = change in temperature.
\( k \) = first-order temperature coefficient of resistance

Thermistors can be classified into two types depending on the sign of \( k \). If \( k \) is positive, the resistance increases with increasing temperature, and the device is called...
a positive temperature coefficient (PTC) thermistor, or posistor. If $k$ is negative, the resistance decreases with increasing temperature, and the device is called a negative temperature coefficient (NTC) thermistor. Resistors that are not thermistors are designed to have a $k$ as close to zero as possible, so that their resistance remains nearly constant over a wide temperature range. PTC thermistors can be used as heating elements in small temperature controlled ovens.

NTC thermistors are used as resistance thermometers in low temperature measurements of the order of 10 K. NTC thermistors can be used also as inrush-current limiting devices in power supply circuits.

They present a higher resistance initially which prevents large currents from flowing at turn-on, and then heat up and become much lower resistance to allow higher current flow during normal operation.

These thermistors are usually much larger than measuring type thermistors, and are purpose designed for this application. Thermistors are also commonly used in modern digital thermostats and to monitor the temperature of battery packs while charging.

They are most commonly made from the oxides of metals such as manganese, cobalt, nickel and copper. The metals are oxidized through a chemical reaction, ground to a fine powder, then compressed and subject to very high heat. Some NTC thermistors are crystallized from semiconducting material such as silicon and germanium.

Thermistors differ from resistance temperature detectors (RTD) in that the material used in a thermistor is generally a ceramic or polymer, while RTDs use pure metals. The temperature response is also different; RTDs are useful over larger temperature ranges, while thermistors typically achieve a higher precision within a limited temperature range [usually -90°C to 130°C].

**Applications:**

- NTC thermistors are used as resistance thermometers in low-temperature measurements of the order of 10 K.
- NTC thermistors can be used as inrush-current limiting devices in power supply circuits. They present a higher resistance initially which prevents large currents from flowing at turn-on, and then heat up and become much lower resistance to allow higher current flow during normal operation. These thermistors are usually much
larger than measuring type thermistors, and are purposely designed for this application.

- NTC thermistors are regularly used in automotive applications. For example, they monitor things like coolant temperature and/or oil temperature inside the engine and provide data to the ECU and, indirectly, to the dashboard.
- Thermistors are also commonly used in modern digital thermostats and to monitor the temperature of battery packs while charging.

**14.4 Experimental Set up:**

![Diagram of experimental setup]

**14.5 Procedure:**

1. The apparatus are placed as it is given in the experimental set up.
2. The thermistor is placed in a vessel containing water and using heater rise the temperature of the water.
3. Find the resistance of the given thermistor at room temperature using multimeter.
4. Repeat the experiment for different temperatures and calculate the temperature co-efficient for various temperatures.
5. A graph was plotted between temperature °C and resistance in ohms of the thermistor.

**14.6 Tabular column:**

<table>
<thead>
<tr>
<th>S.No</th>
<th>Temperature °C</th>
<th>Resistance in ohms</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.</td>
<td></td>
<td></td>
</tr>
<tr>
<td>2.</td>
<td></td>
<td></td>
</tr>
<tr>
<td>3.</td>
<td></td>
<td></td>
</tr>
<tr>
<td>4.</td>
<td></td>
<td></td>
</tr>
<tr>
<td>5.</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
14.7 Model graph:

![Graph showing resistance in ohms vs temperature in °C]

14.8 Result:
Thus the given thermistor characteristics were measured and verified.

14.9 Pre Lab questions:
1. What is meant by temperature sensor and what are the types of temperature sensors?
2. What is meant by positive and negative temperature coefficient of resistance?
3. Give the differences between active and passive transducers?
4. What is a thermistor and how it is made?

14.10 Post Lab Questions:
1. List the applications of thermistors?
2. Compare thermistor with RTD and thermocouple.
3. Thermistor is a passive transducer? Justify.